



2009 LCW

Paul Rubinov

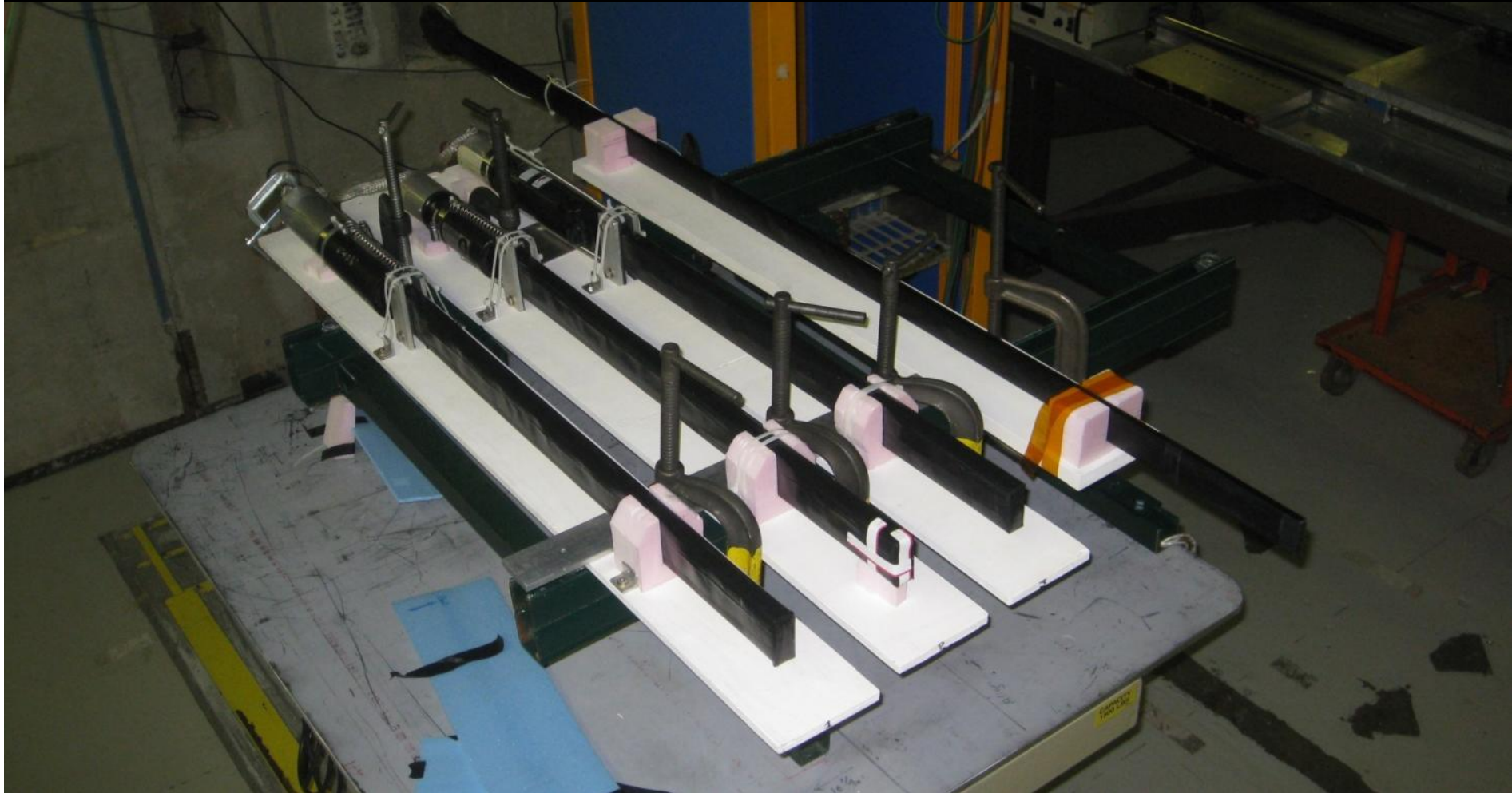
Fermilab



PLANS FOR MUON/TAIL CATCHER TEST BEAM AT FERMILAB

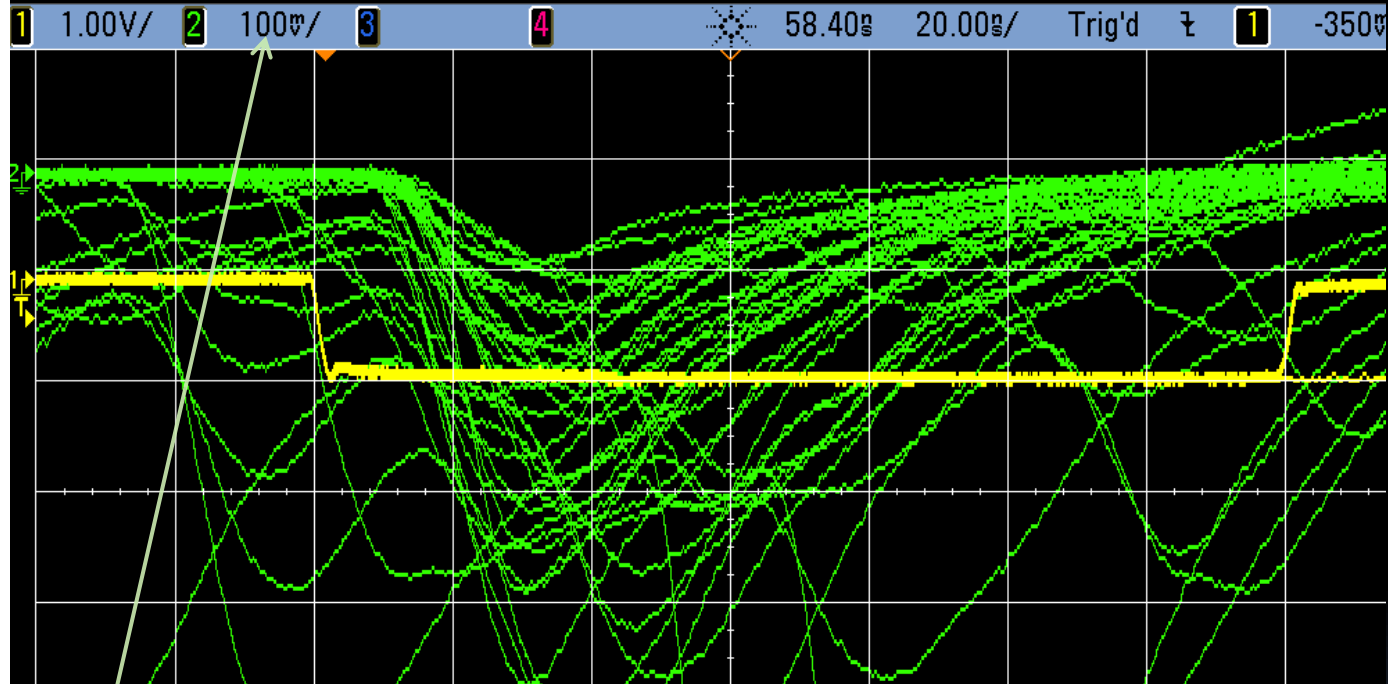
Previously, at MT6

- We did a quick run in 2008 (parasitic with Minerva)



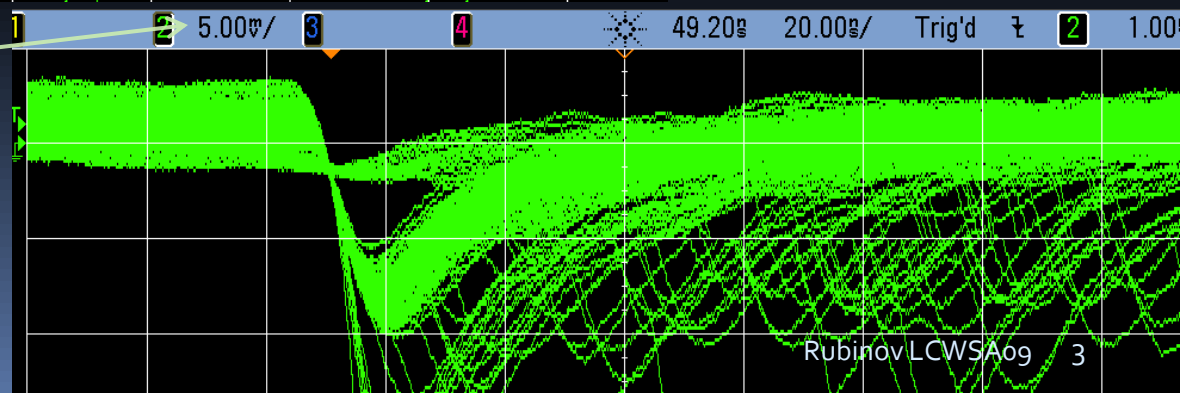
From testbeam

- ~100% Efficient?! A few hundred traces from 1 spill



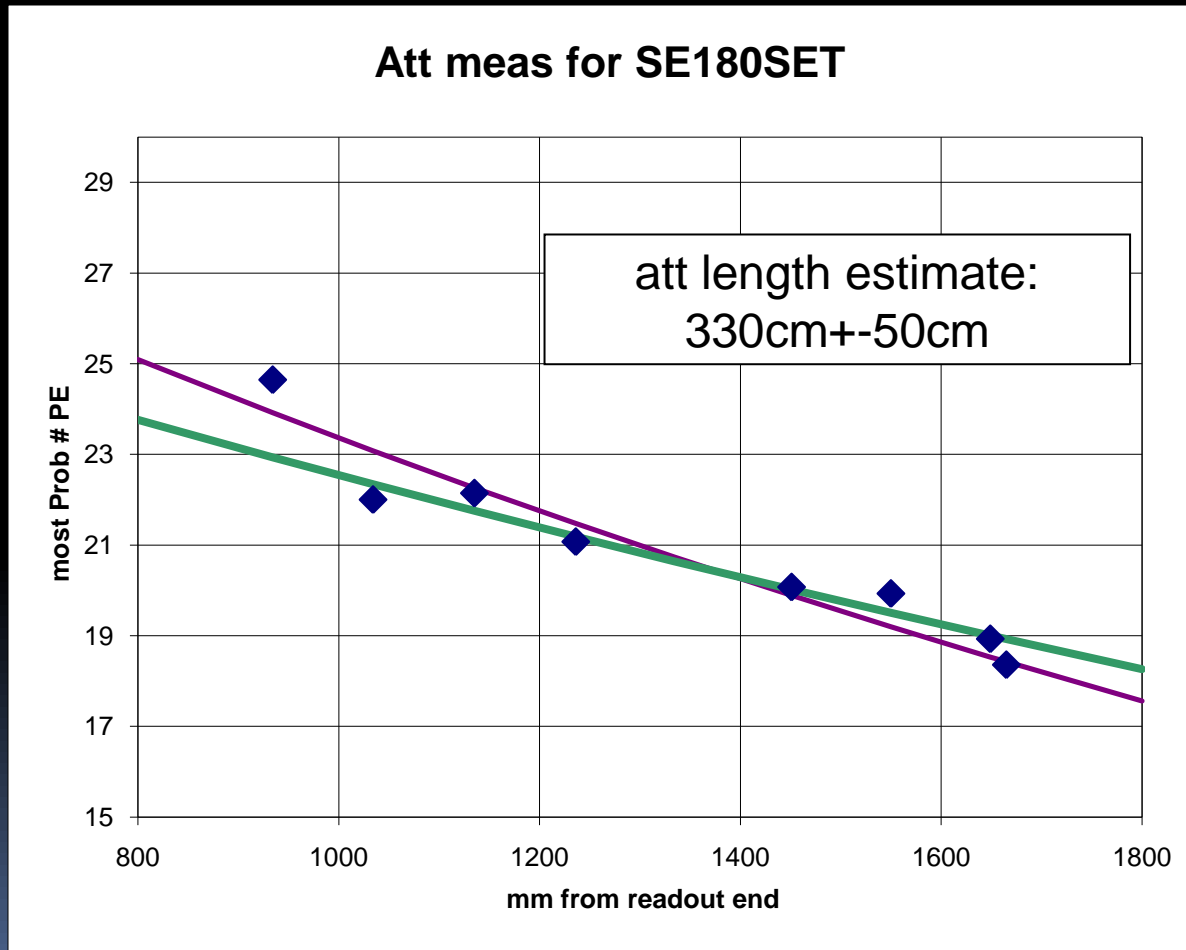
Noise

Don't miss the scale change!



From testbeam

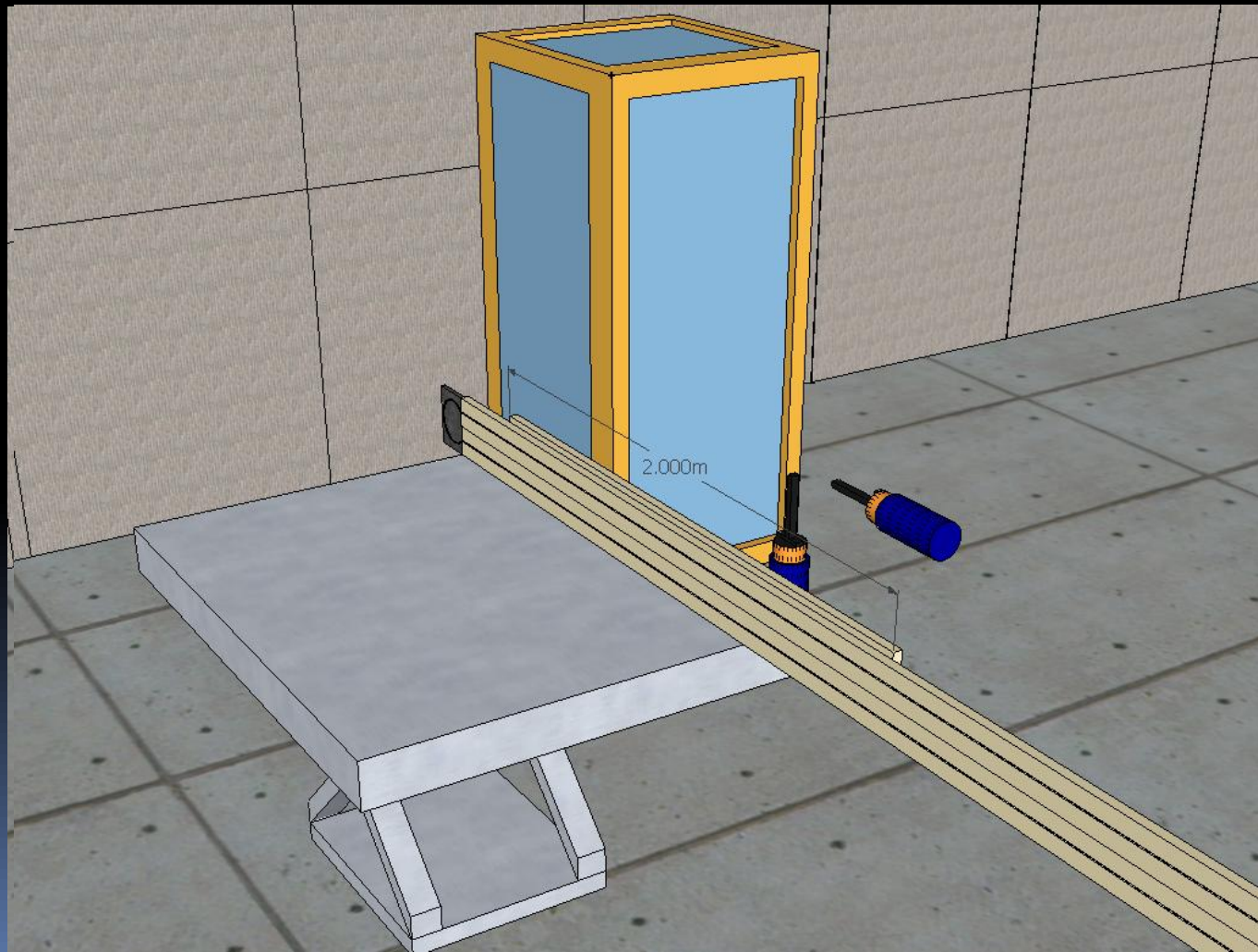
- We even tried to measure attenuation



Need more lever
arm!

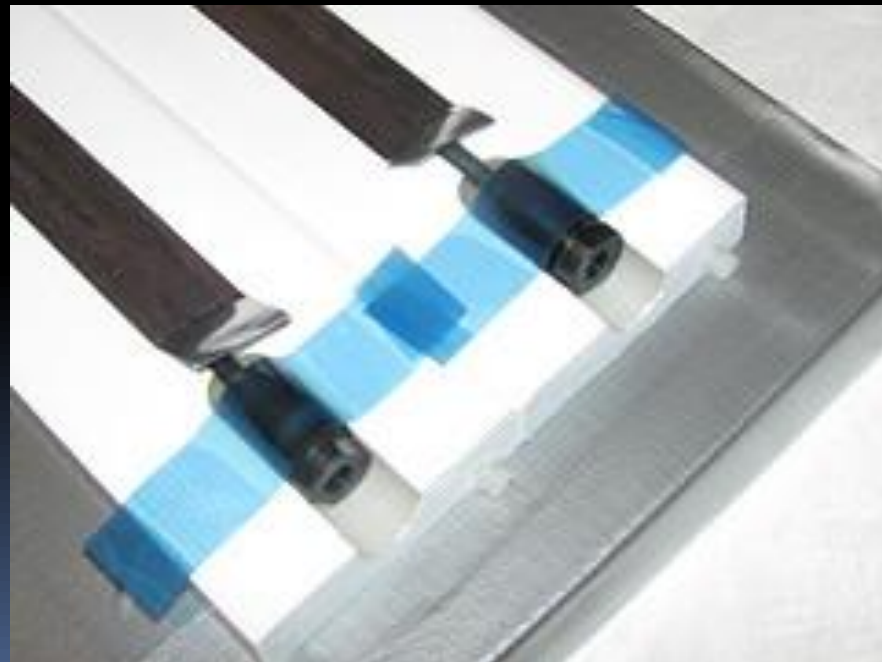
From testbeam

- Sketch of the TB 2008 setup



New tests

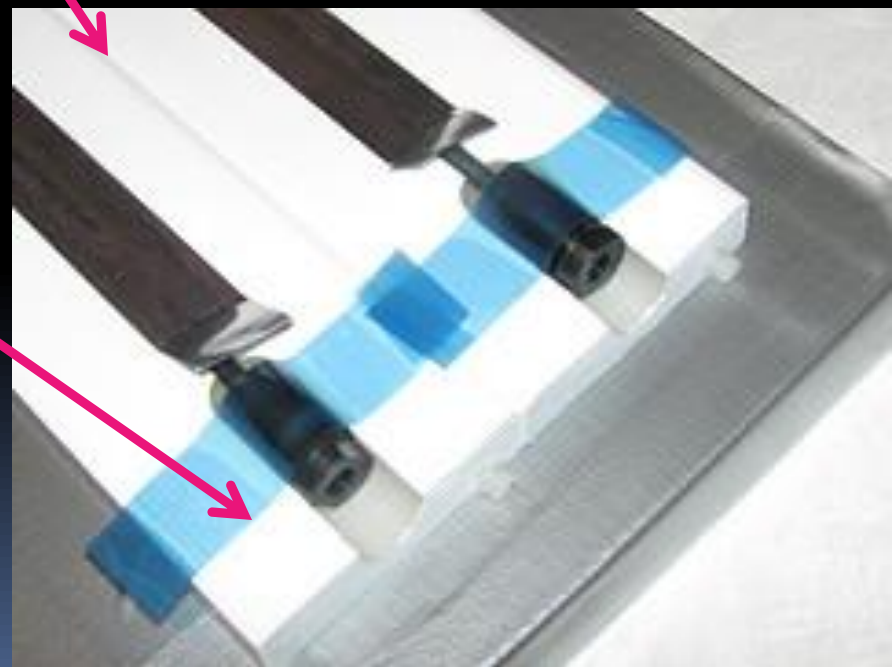
- Want to measure
 - More channels
 - Much longer strips (284 inches)
 - Double ended readout



New tests

- Losses in the crack between adjacent strips
- Losses in scint behind SiPM

**MUST KNOW THE
POSITION OF
PARTICLES PRECISELY**



Do we need tracking for Muon TB

- NO

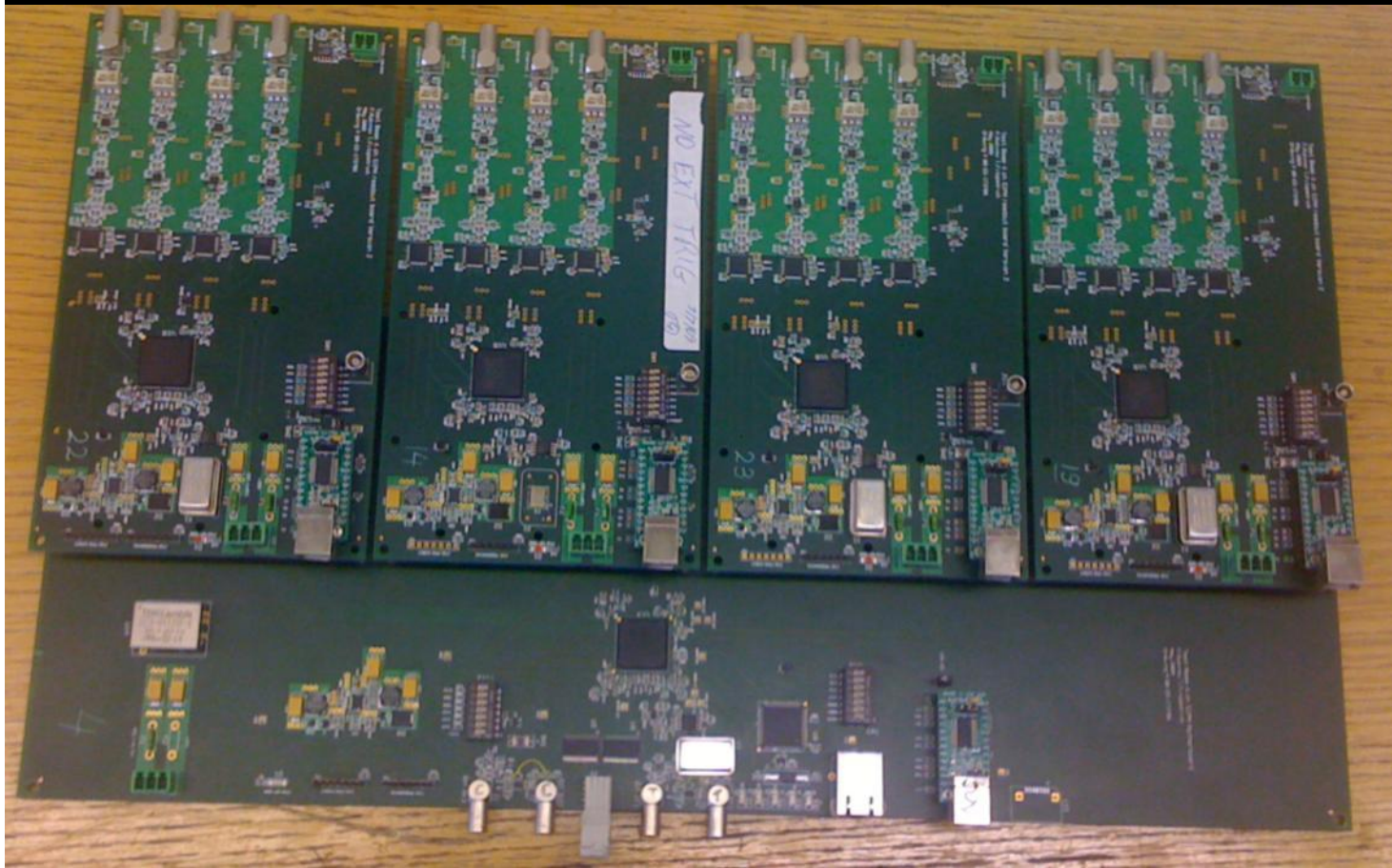
- Heterogeneous system – everything different
- Num of channels goes from 16 or 32 to 1016 or 1032
- I'm scared of tracking because I'm a wimp

- YES

- Very good position resolution without hurting rate
- Very good two track rejection
- Powerful tool that can be used in future studies
 - E.g. testing of dual readout crystals
- I'm scared of tracking because I'm a wimp

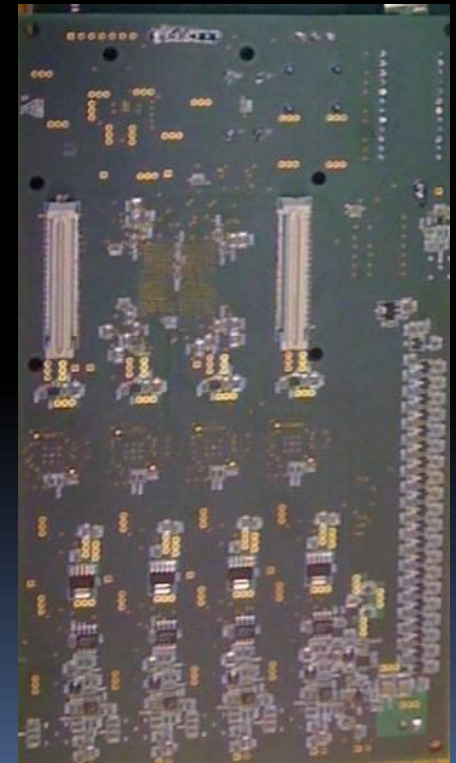
New tools

- New strips
- New electronics – my main emphasis



New since LCW08

- Our plan for readout was (and is)
 - Fall 08: just an amplifier in a NIM bin using 500hm cables
 - Spring 09: Integrate amp, ADC, bias on one board
 - Fall 10?: SiPM readout ASIC
- New electronics ready to go for TB
 - A board that strikes a good balance of high performance and reasonable cost to support SiPM studies
 - self sufficient, simple to use and flexible
 - reuse known designs whenever possible.



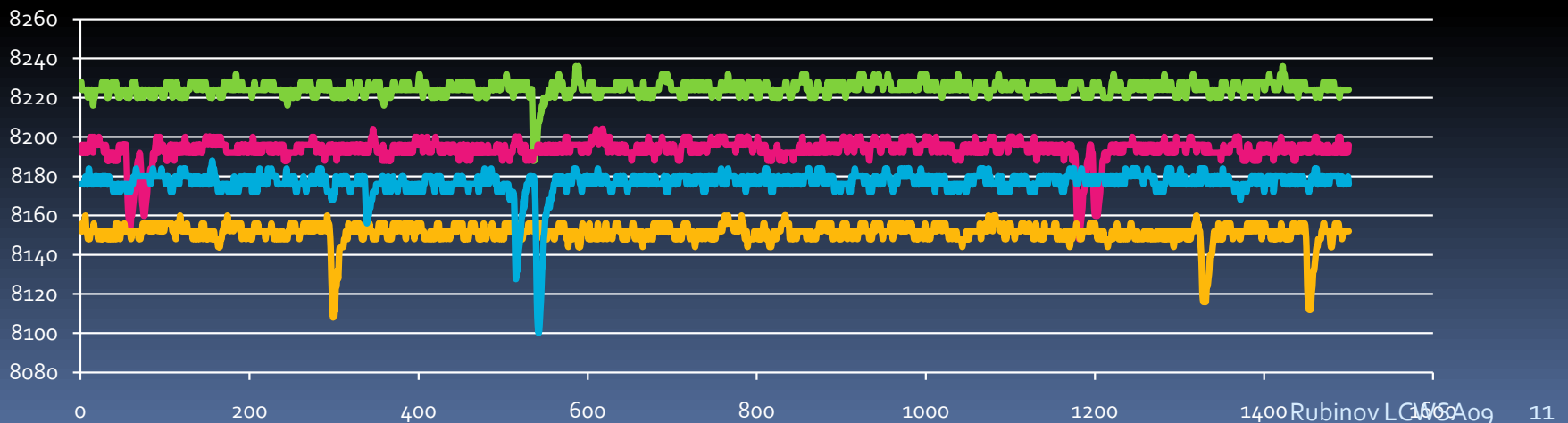
TB4

TB4 key features

- Works like a 4ch of digital scope, but one that has a 0.5mV/DIV scale and precision 100V power supply

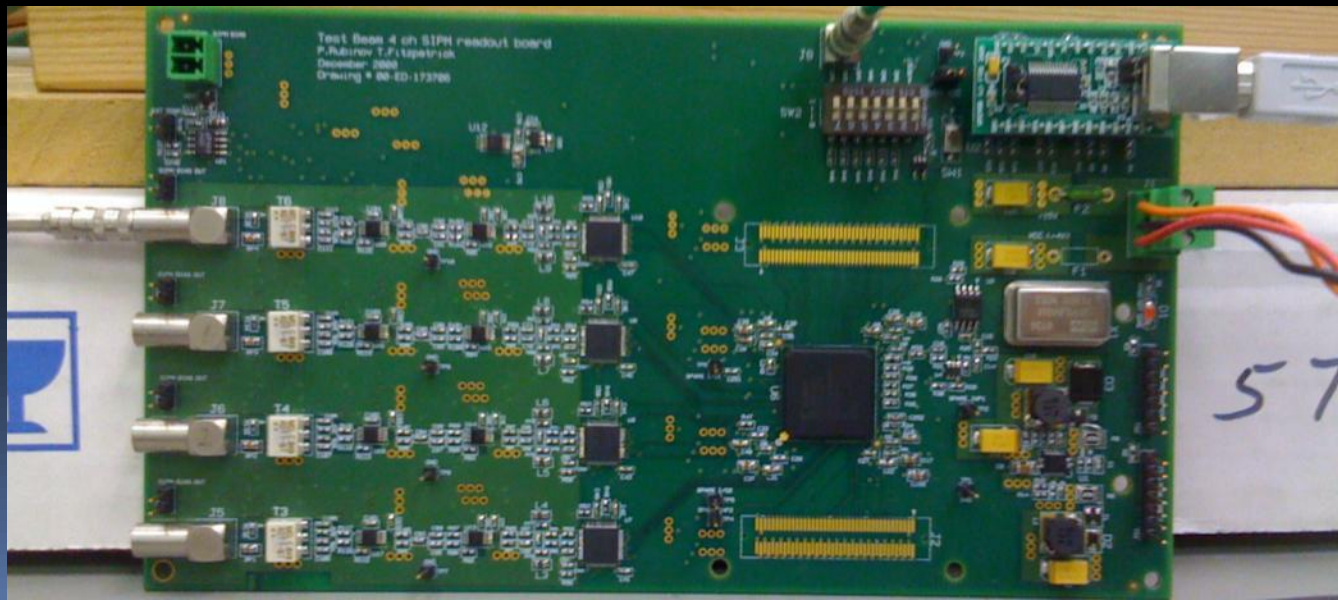
~\$1K for
210MSPS 12bit
~\$1.2K for 14bit

- 12 or 14 bit, 210 or 250 MSPS, gain up to ~40db
- Largish FPGA (with 4kpts memory/ch)
- USB interface, High Speed i/o
- On board bias generation for SiPMs (and current meas)



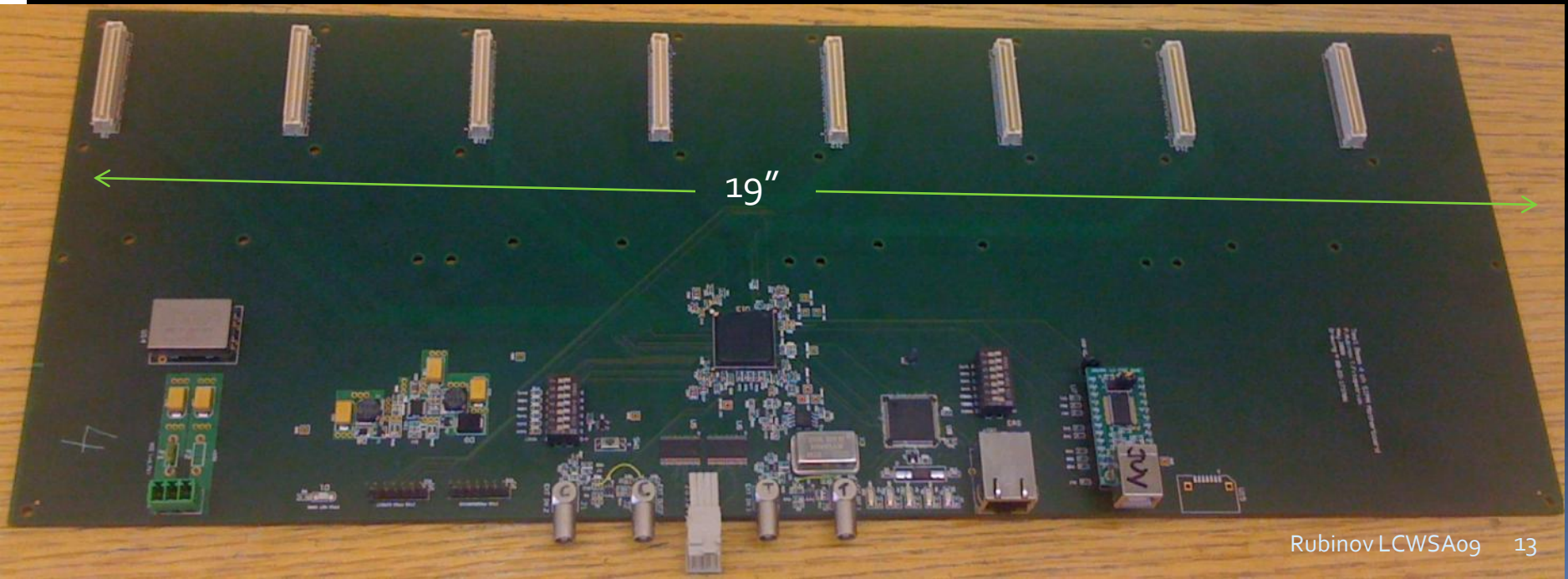
Emphasis on simple

- Plug in 5V/15V power
- Plug in SiPM into an end of a 50 ohm cable
- Plug the other end of the cable into the TB4 board
- Plug in the USB connector into your computer
- Start the software, and press the RUN button



TB4 continued

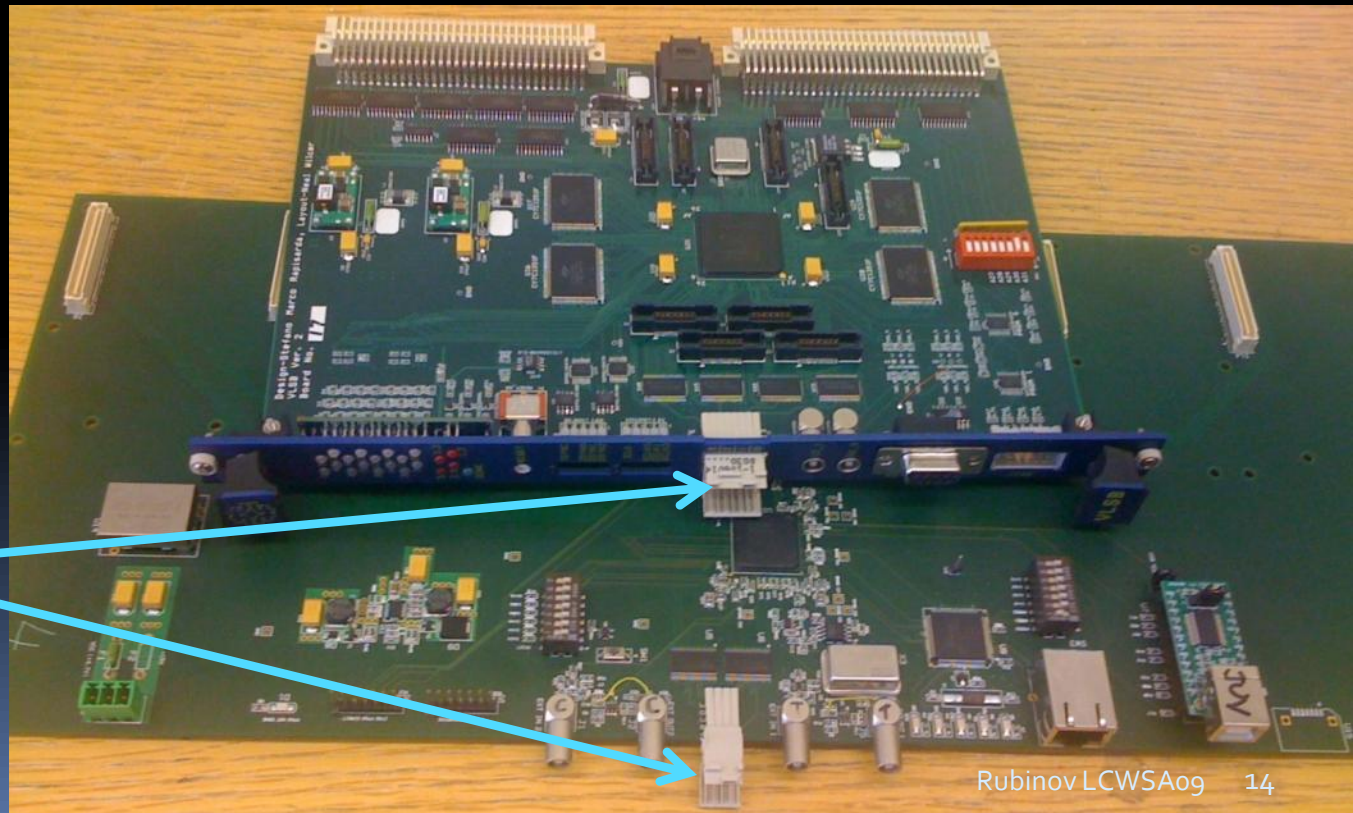
- For slightly larger applications, like test beam
 - 4xTB4 combined on 1 motherboard
 - Mother board provides:
 - Ethernet interface, USB interface, triggering, clocking
 - High speed LVDS (2 x 1 Gbps)

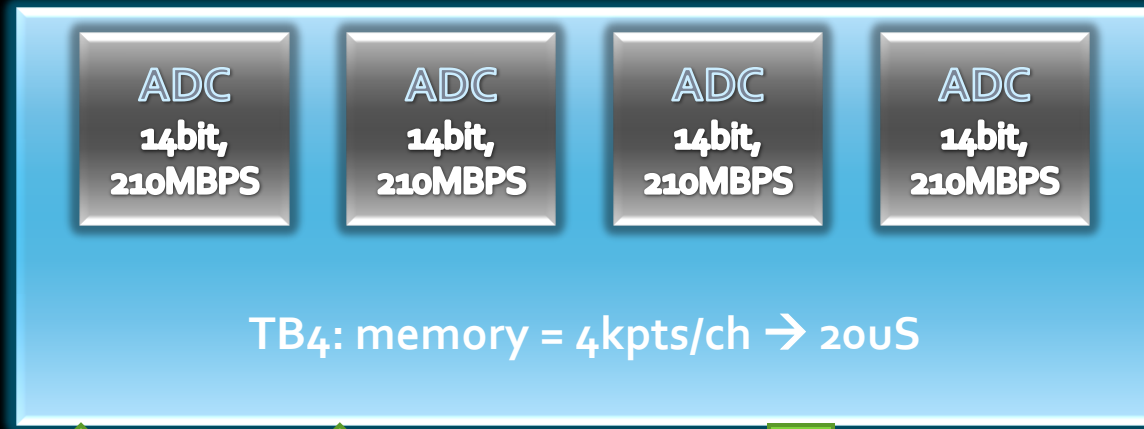


TB4 continued

- For fast readout: LVDS links (2 x 1 Gbps) go to a VME module (1 module has 4 links) with sufficient memory (512KB) to act as a buffer for better throughput

LVDS links run from MB to VLSB
(old Dzero module left over from AFE2 project)





trig
clk



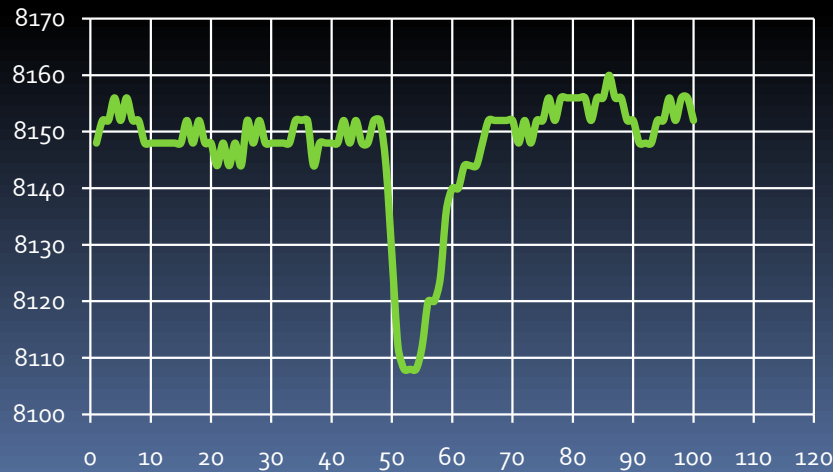
USB

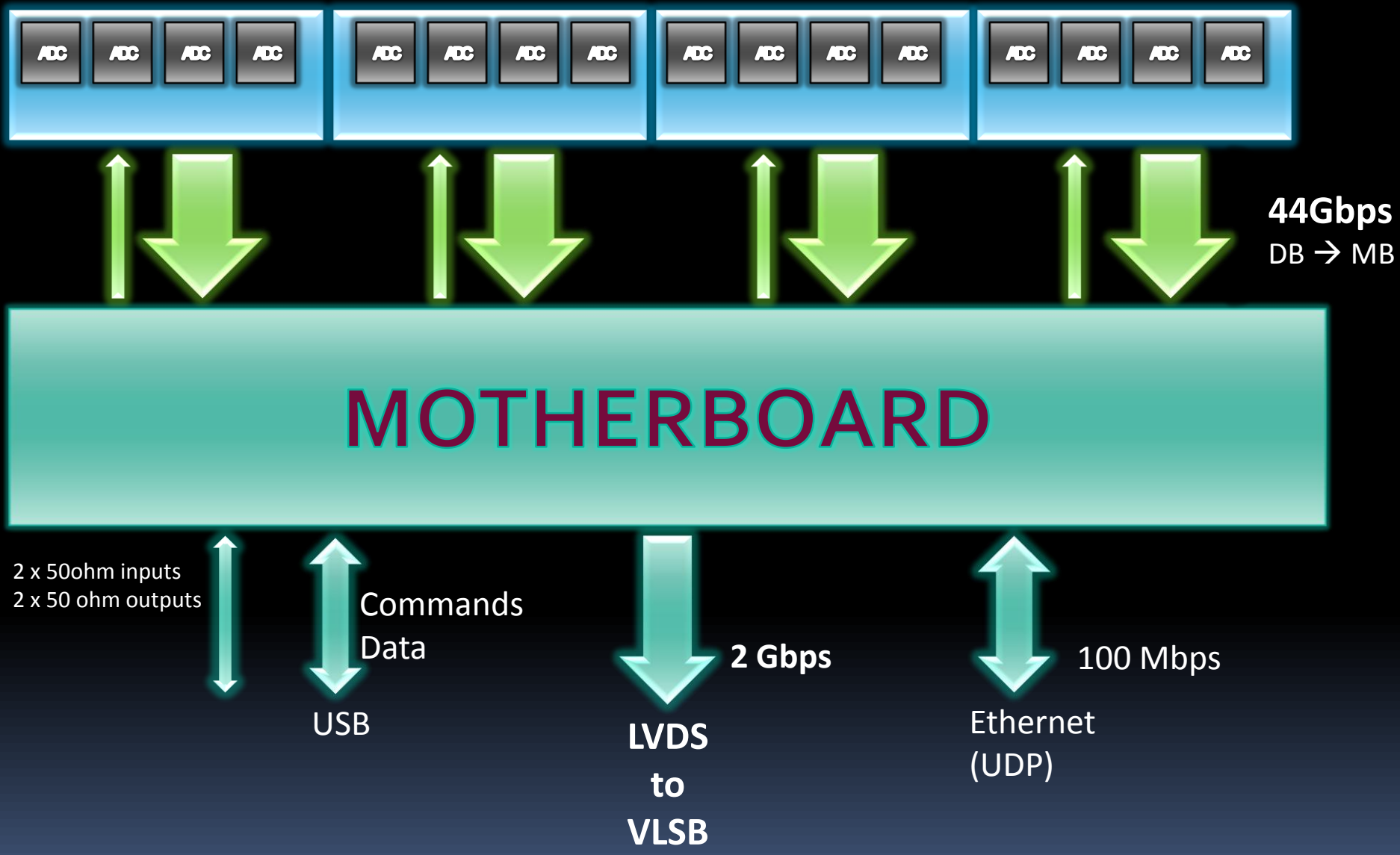
Commands
Data



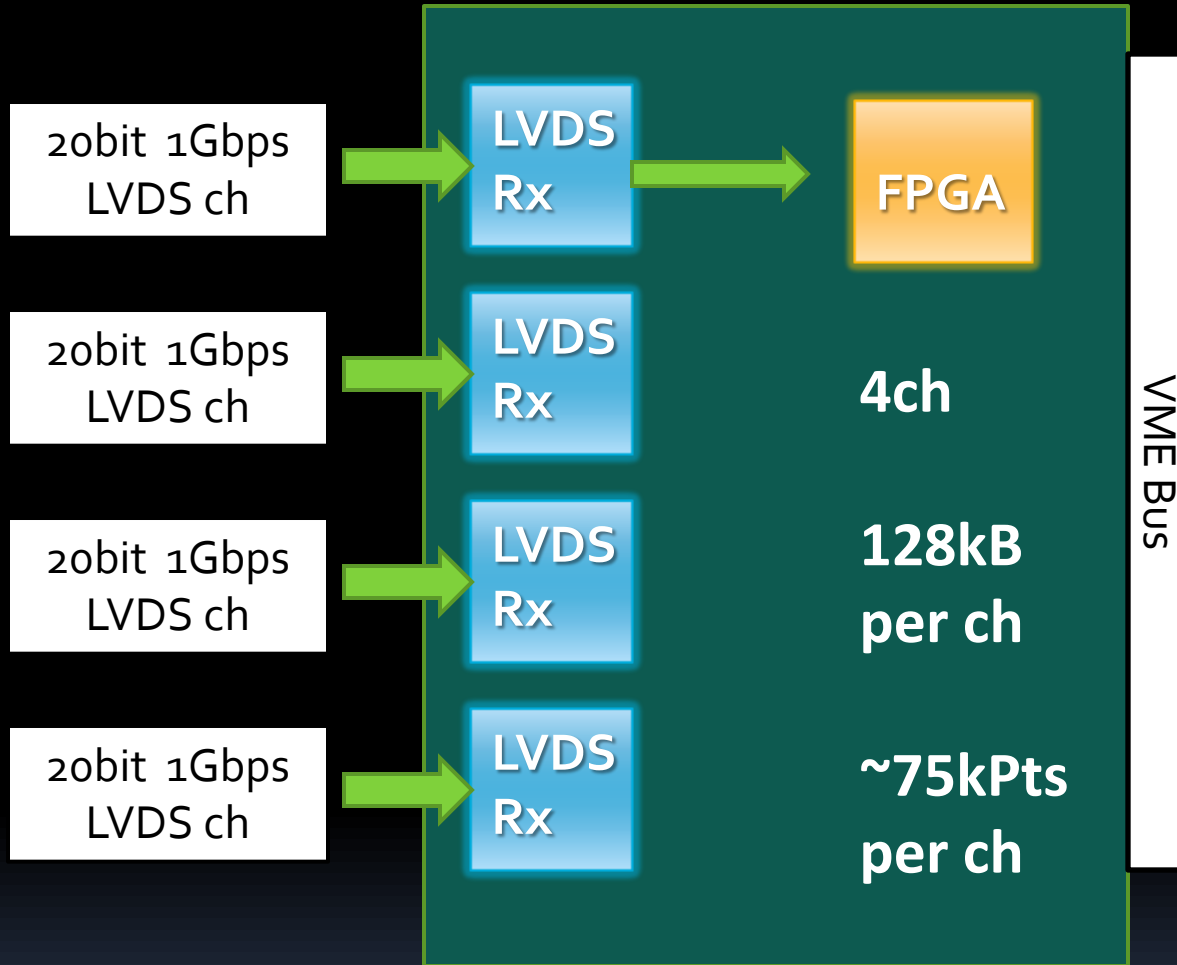
Internal bus

2.8Gbps/ch
11Gbps per TB4





VLSB



VLSB can buffer 300k Samples

Numerology

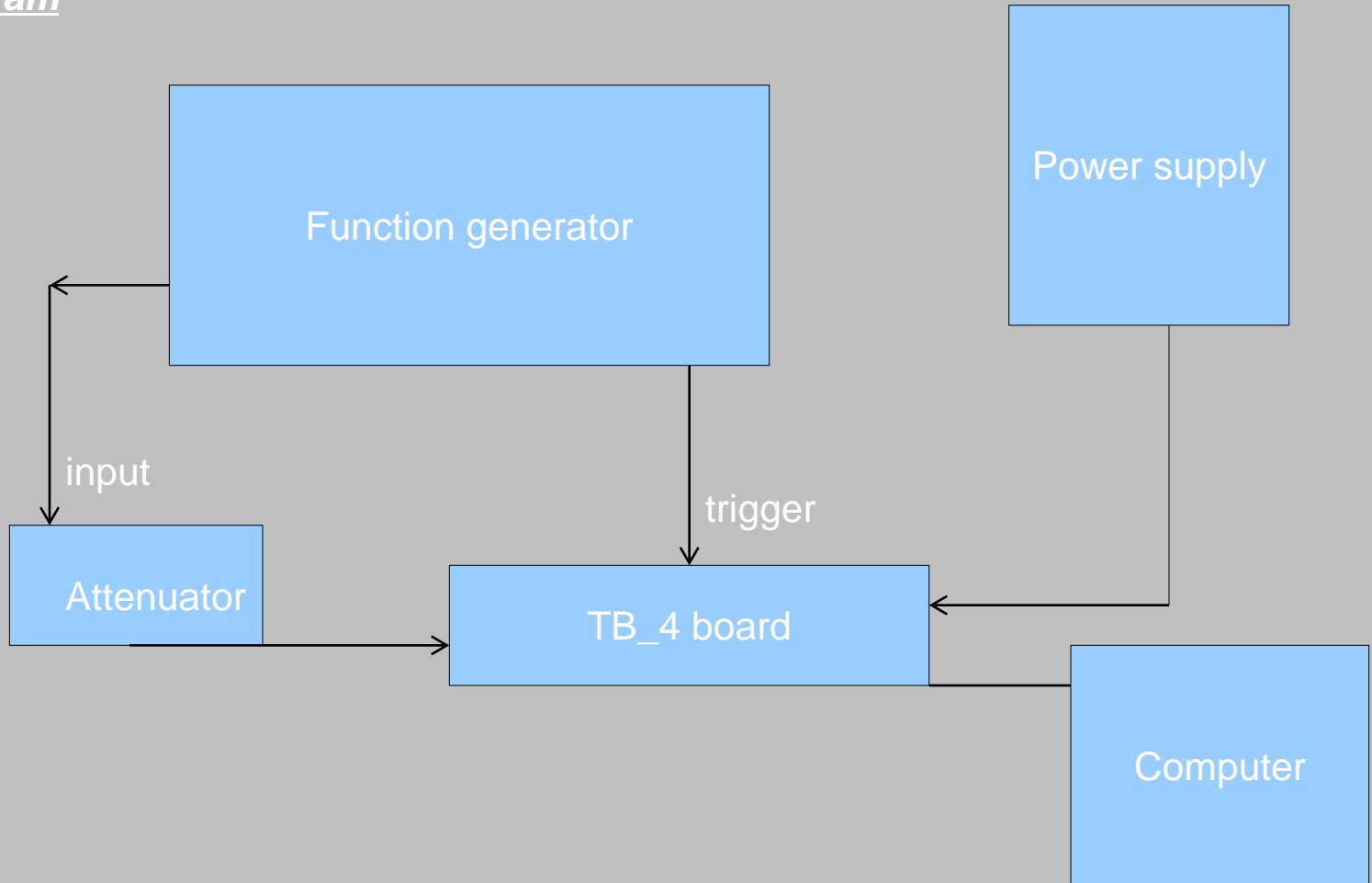
- Realistically for TB:
 - 16ch \rightarrow 1MB
 - \sim 100 pts per trig storage
 - 1 MB and 1 VLSB with 2 links
 - Can store about 180 triggers
 - read only between spills
- Worst case
 - Assume \sim 200 pts/ch per trig
 - 2 Motherboards per VLSB (means VLSB can buffer 45 trig)
- Decent readout during spill (\sim 10MB/s over VME32) to get \sim 100Hz rate required

Needs and next steps

- Muon beam, by its nature, is easy to share
 - We need to reach out to other potential users
- Complete MOU with Fermilab TBF
 - Formalize our needs and institutional responsibilities

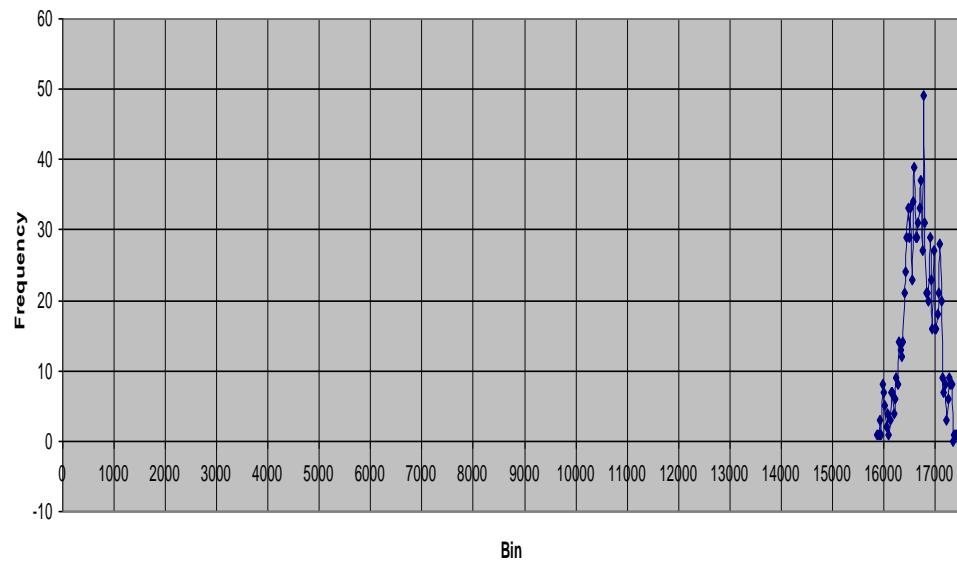
END OF TALK

Block Diagram

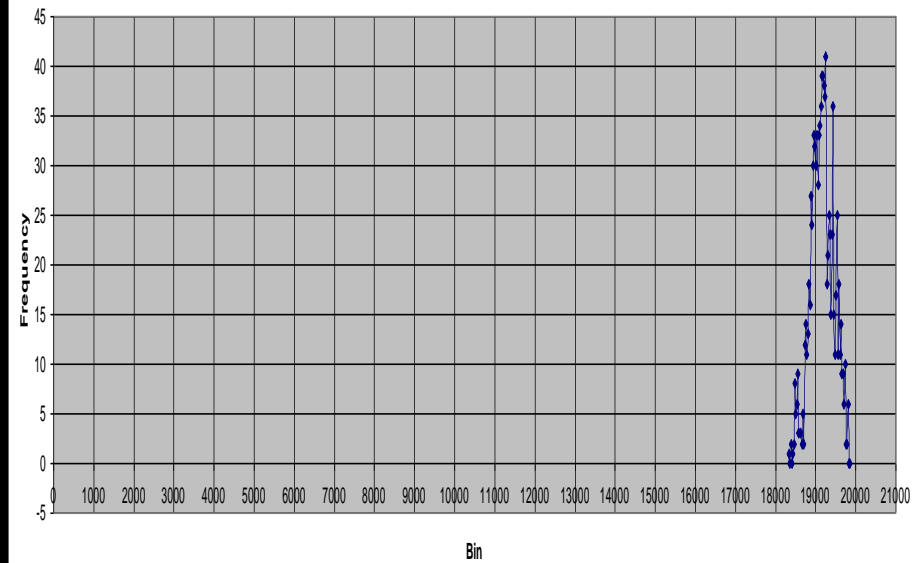


Function Generator: Tektronix AFG 3252
Power Supply : Kenwood

2.7V;10ns



3.1V;10ns



Amplitude
(V)

Input Charge
(pC)

Mean charge Counts
(ADC)

1ADC
(fC)

0.25

0.5

1057.00

0.331

0.5

1.0

3324.15

0.300

1.7

3.4

10550.00

0.322

2.3

4.6

14216.00

0.323

2.7

5.4

16688.50

0.323

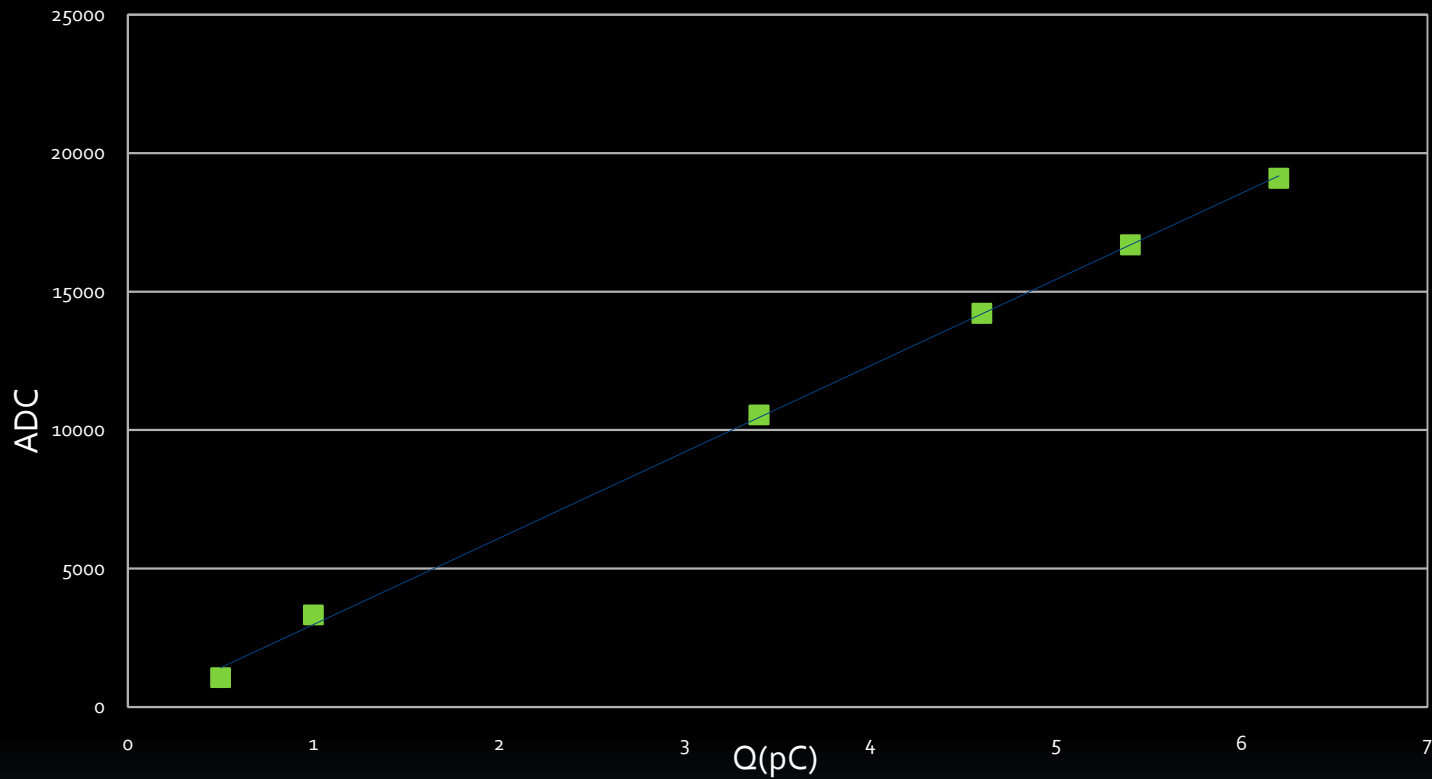
3.1

6.2

19094.50

0.324

ADC VS Q

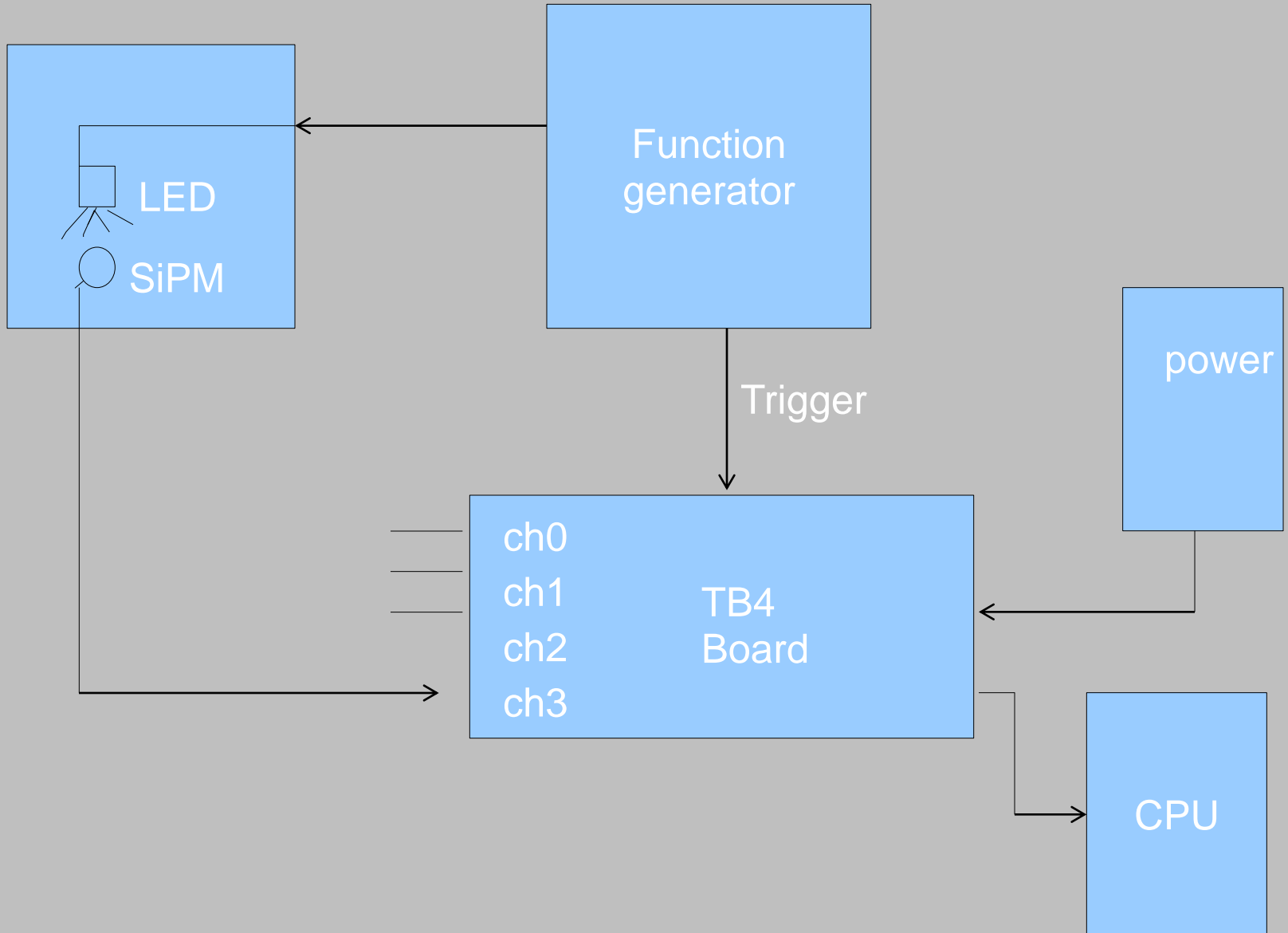


Inverse of the slope gives charge per channel

$$(\text{slope})^{-1} = 0.329\text{fC/Channel}$$

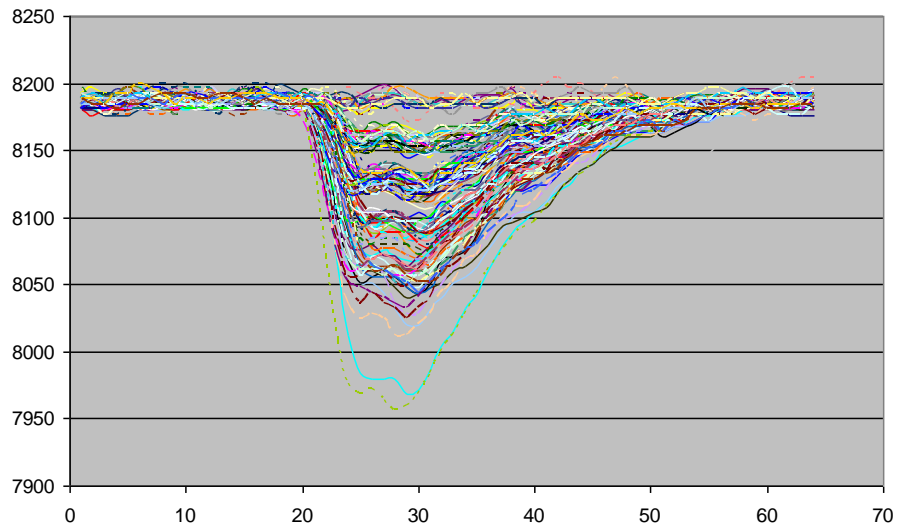
Therefore, 1ADC count = 0.329fC

Block Diagram

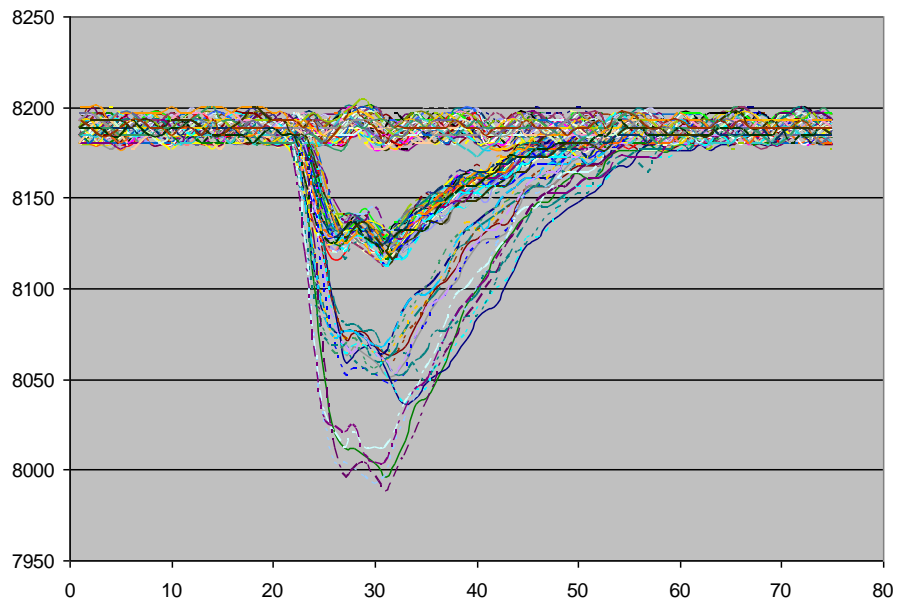
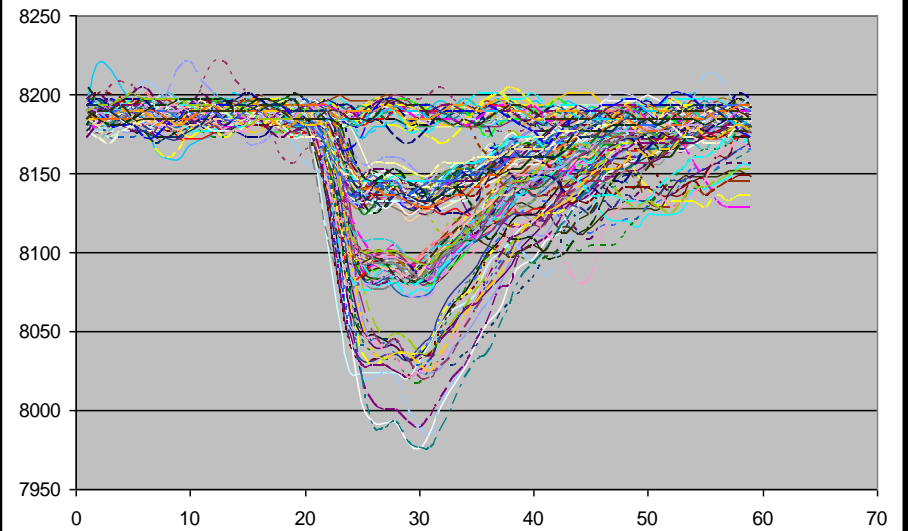


Hamamatsu100 SiPM Plots and Gain calculations

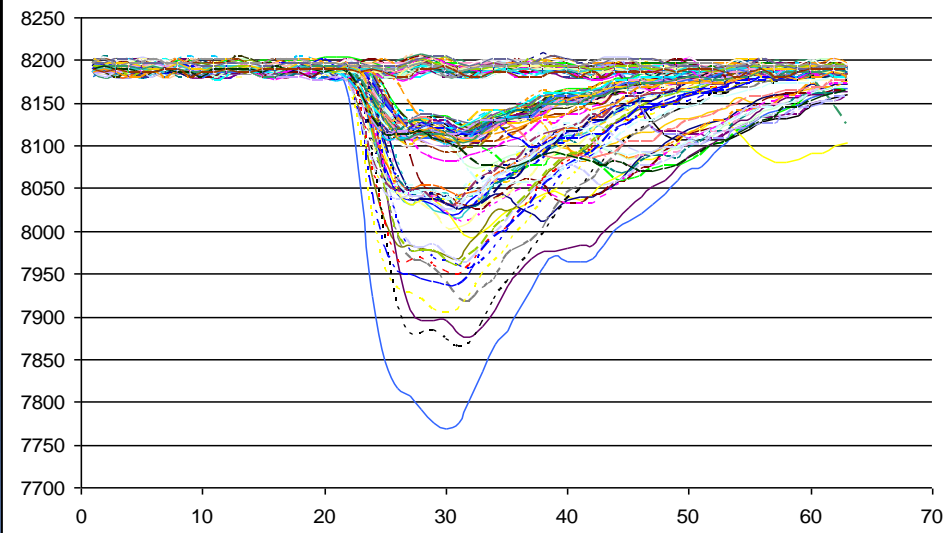
raw data 68.9V

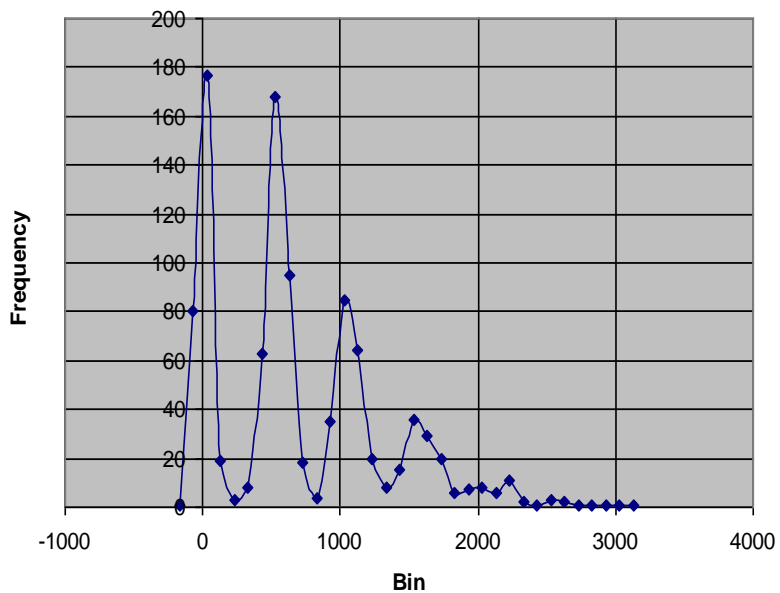
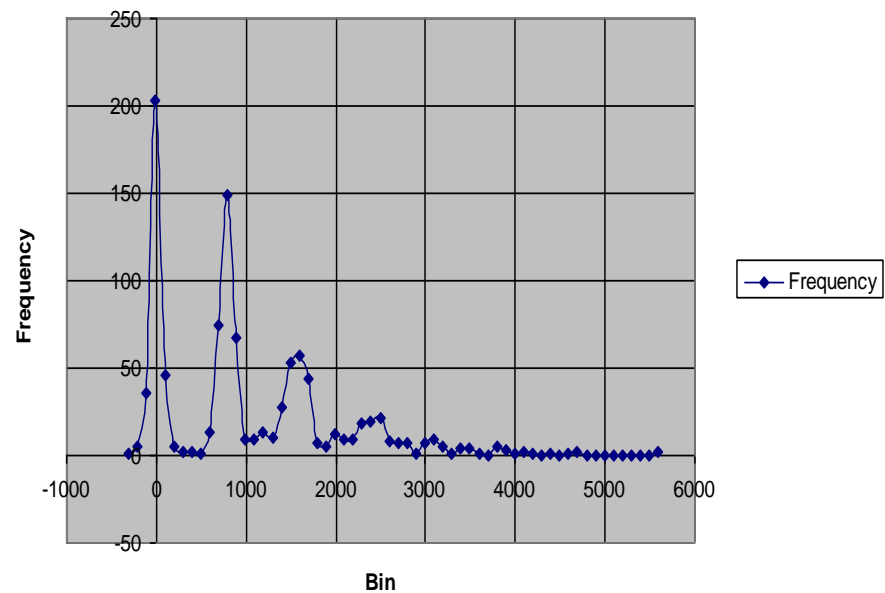
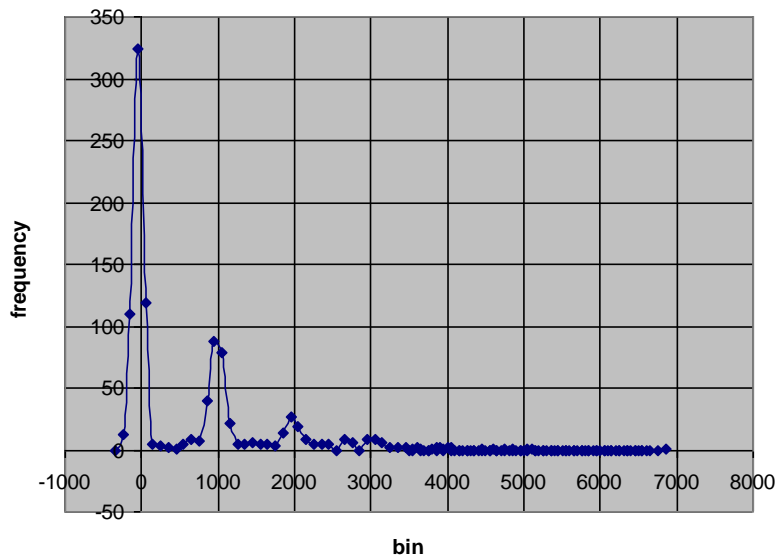
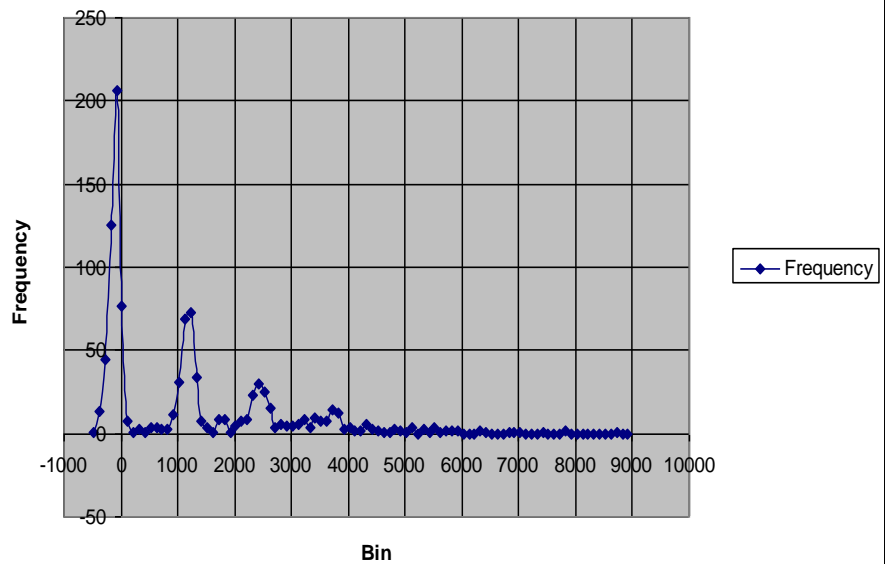


69.1V

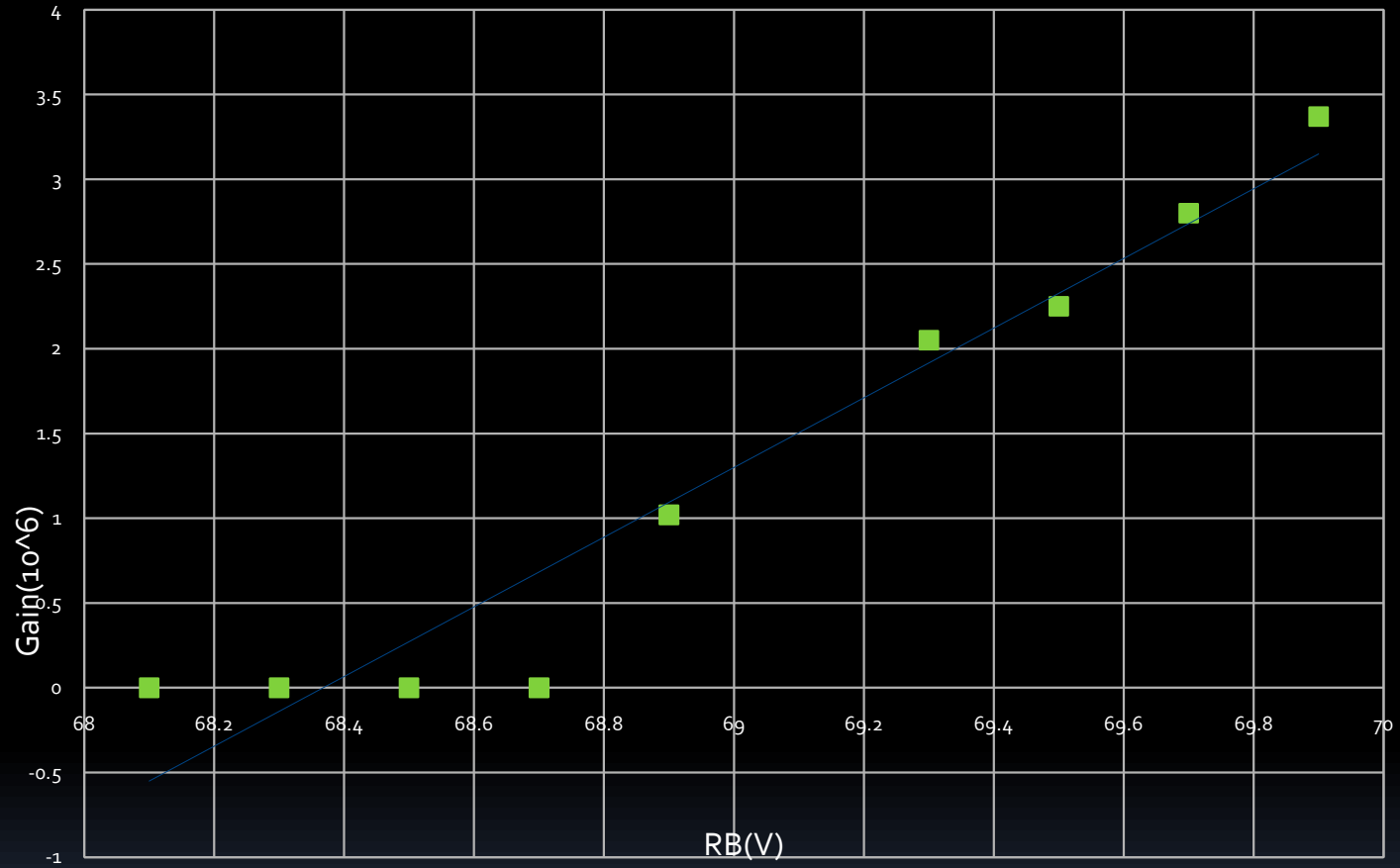


raw data 69.5V



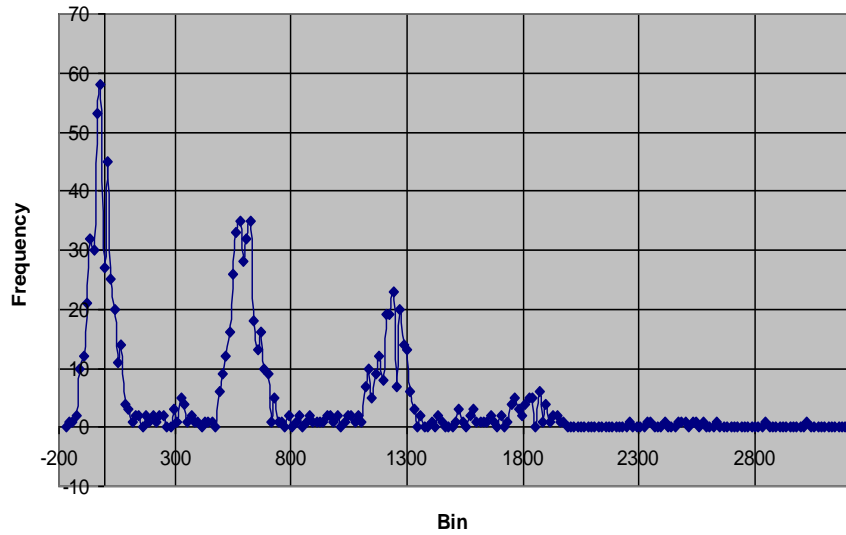
68.9V**69.1V****69.3V****69.5V**

Gain vs Reverse Bias Voltage

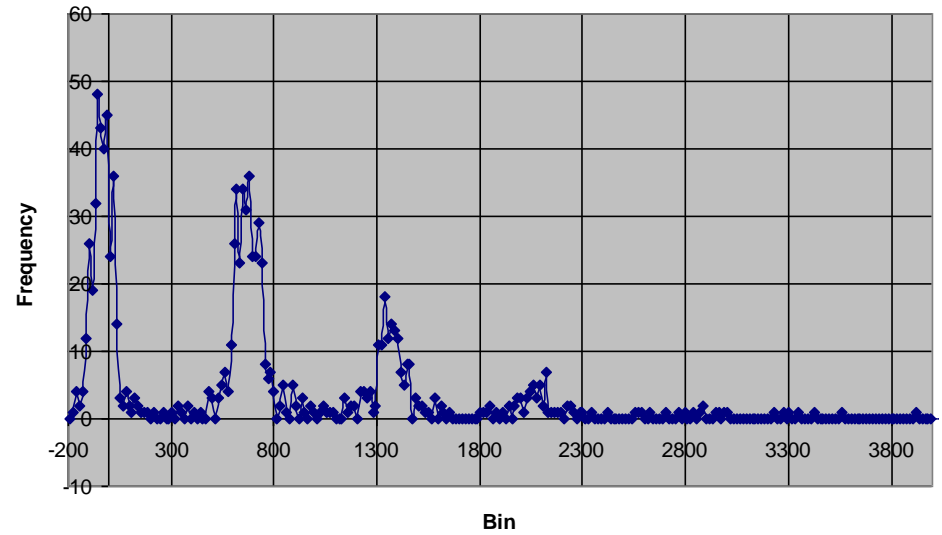


SenSL devices (1mm x 1mm)

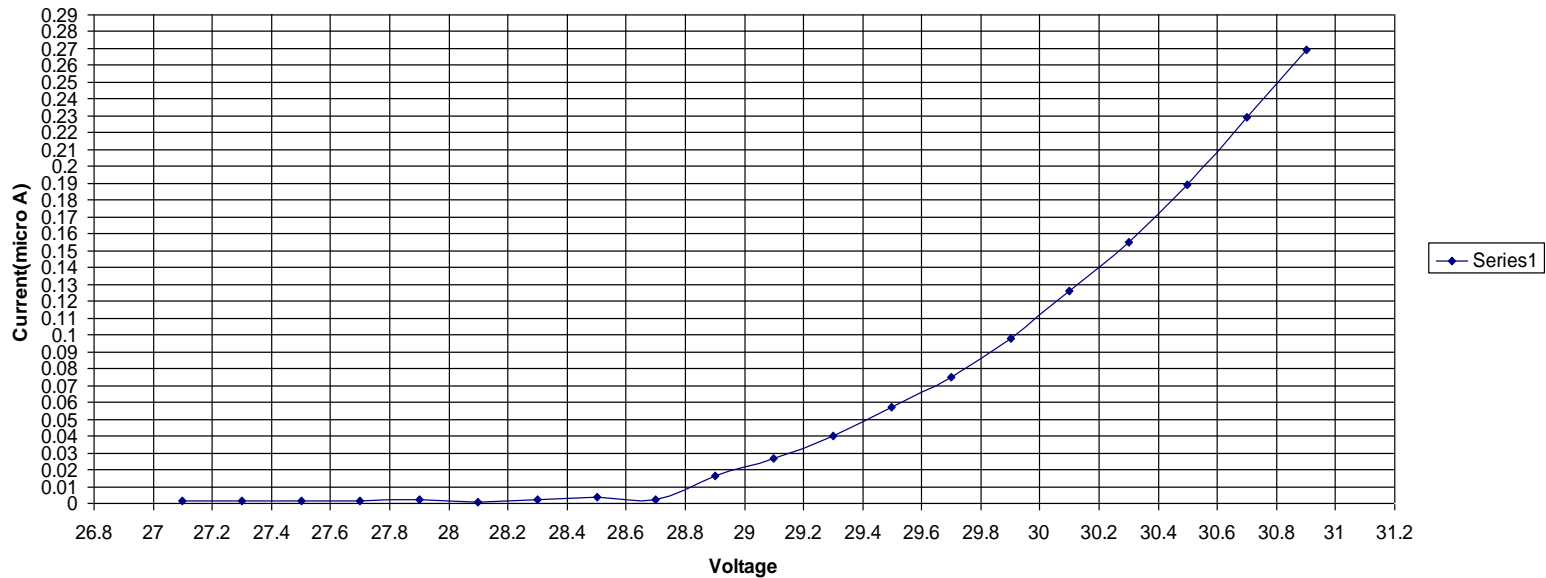
30.3V



30.5V

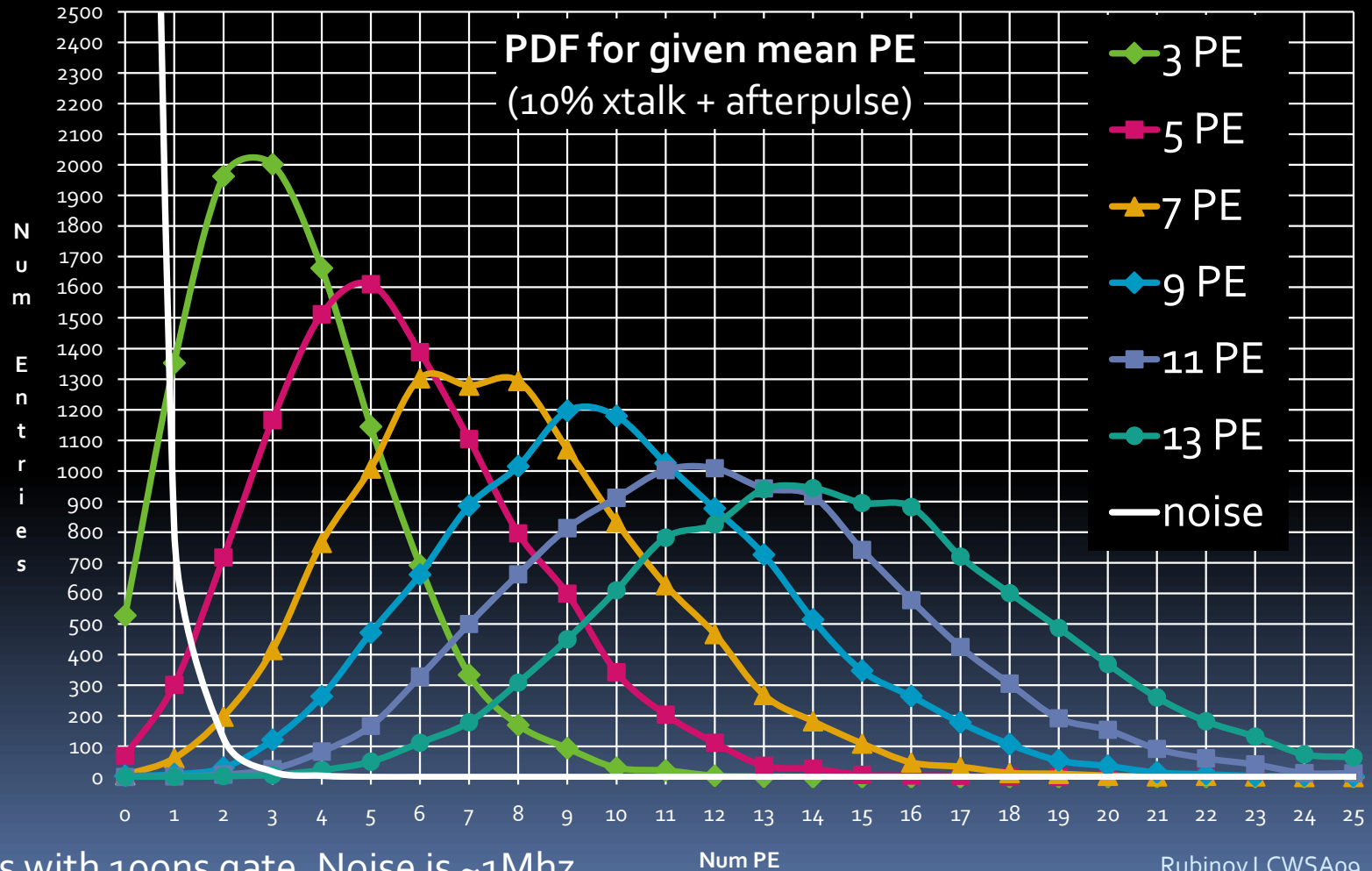


Current Vs Voltage



Photon Statistics

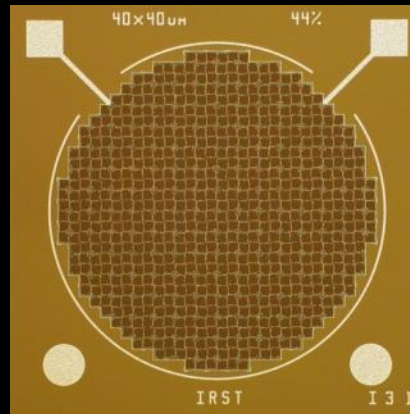
- This is the ultimate limit for noise/efficiency



This is with 100ns gate. Noise is ~1Mhz

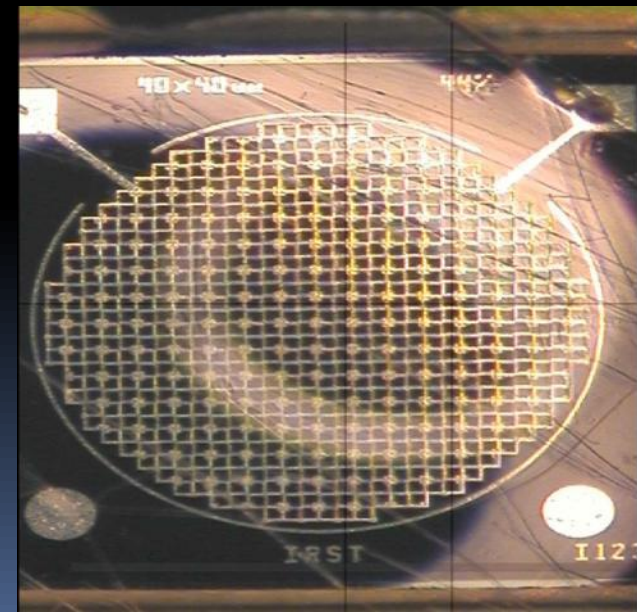
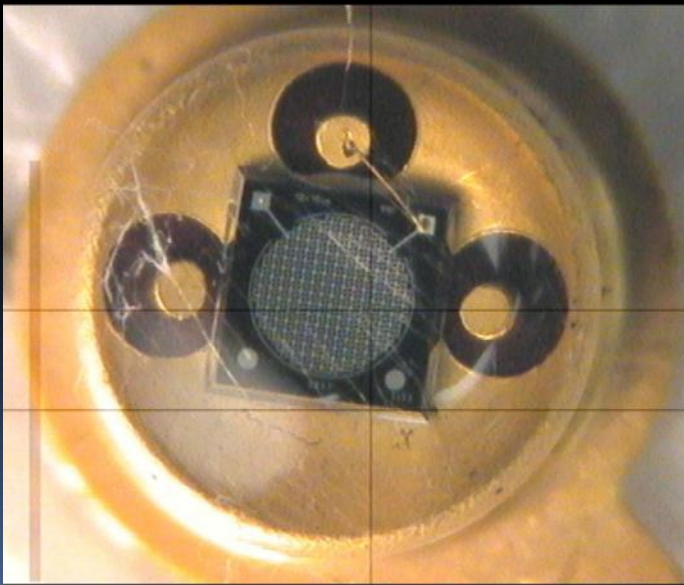
IRST SiPMs for muon-counter/tailcatcher application study at FNAL

On commission from INFN Udine/Trieste, SiPMs have been produced by FBK-IRST (Trento, Italy) for this application.



Geometry: circular
diameter: 1.2 mm
Microcell: $40 \times 40 \mu\text{m}$
Improved fill-factor (44%)
Breakdown voltage $\sim 30.5\text{V}$

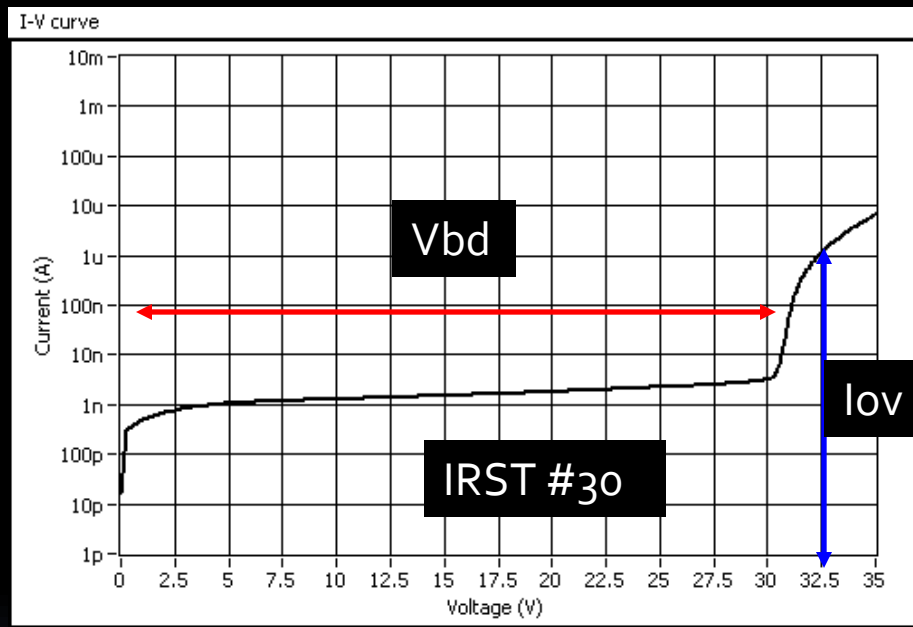
They are presently packaged (To18) with photocathode protected by epoxy(glob-top)



Bench Tests

reveal :

- Low operating voltage (~30V)
- Relatively large operating range (5V)
- very uniform characteristics



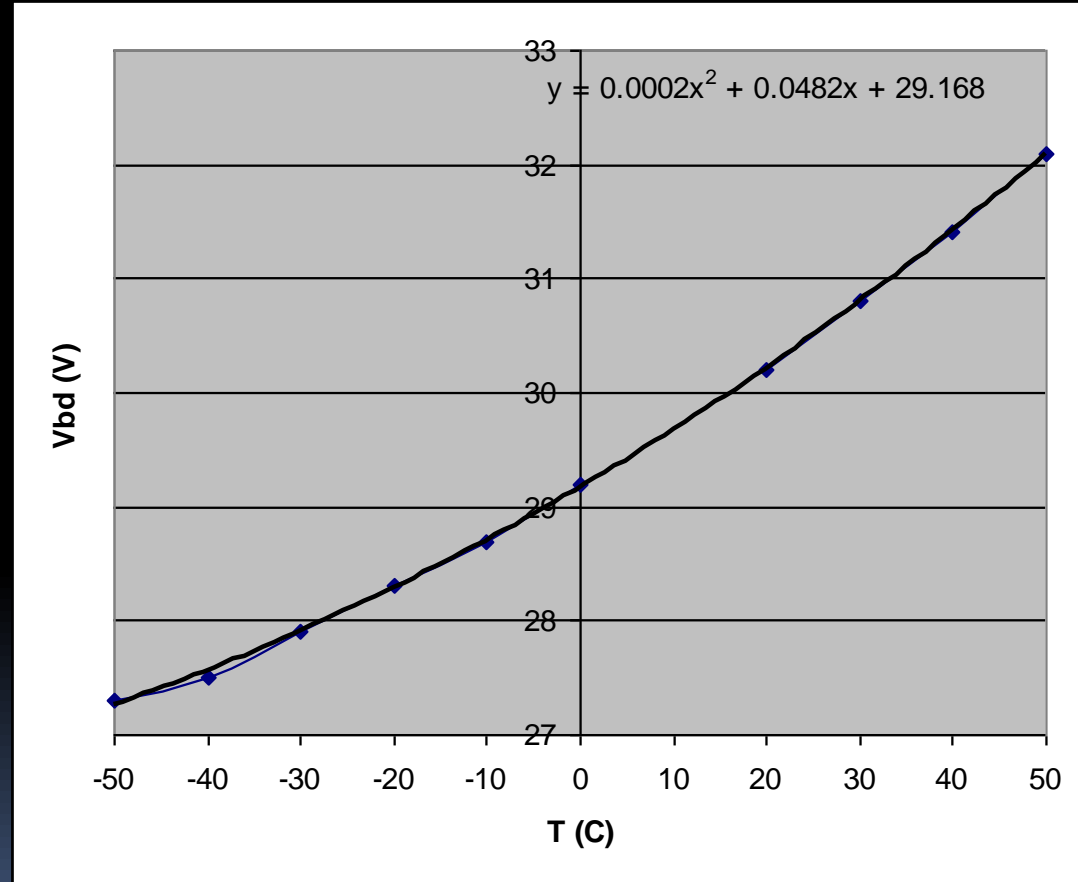
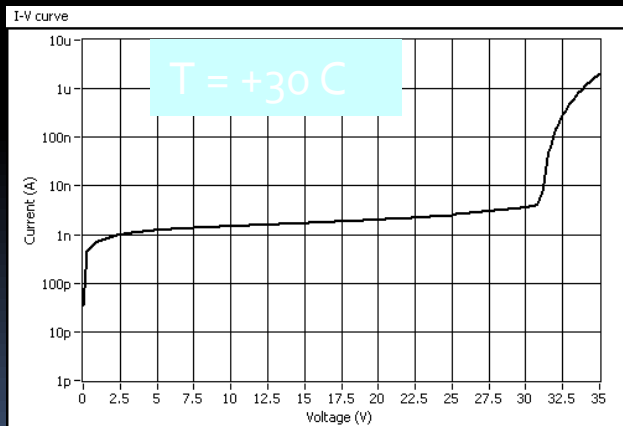
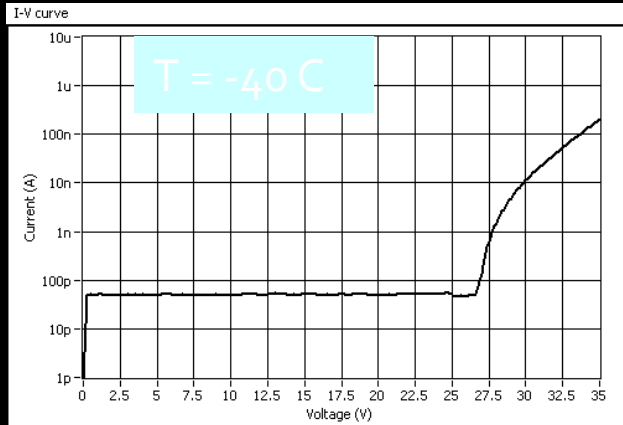
| SiPM # | Vbd (V) | lov (uA) |
|--------|---------|----------|
| 30 | 30.4 | 4.7 |
| 31 | 30.4 | 3.5 |
| 32 | 30.5 | 3.2 |
| 33 | 30.6 | 3.9 |
| 34 | 30.5 | 3.8 |
| 35 | 30.5 | 3.7 |
| 36 | 30.6 | 4.7 |
| 37 | 30.5 | 5.2 |
| 38 | 30.3 | 4.6 |
| 39 | bad | bad |
| 40 | 30.4 | 4.3 |
| 41 | 30.6 | 2.2 |
| 42 | 30.6 | 1.8 |
| 43 | 30.7 | 3.5 |
| 44 | 30.7 | 3.2 |
| 45 | 31.7 | 4 |
| 46 | 30.3 | 1.9 |
| 47 | 30.3 | 2.7 |
| 48 | 30.3 | 2.8 |
| 49 | 30.4 | 1.7 |
| 50 | 30.3 | 4.9 |

Test beam (fnal: T956)

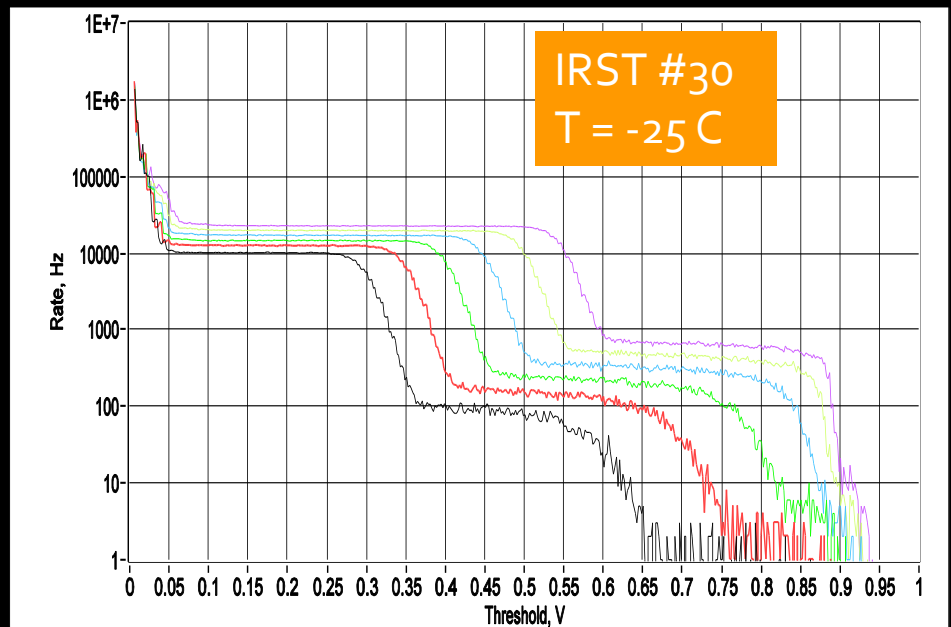
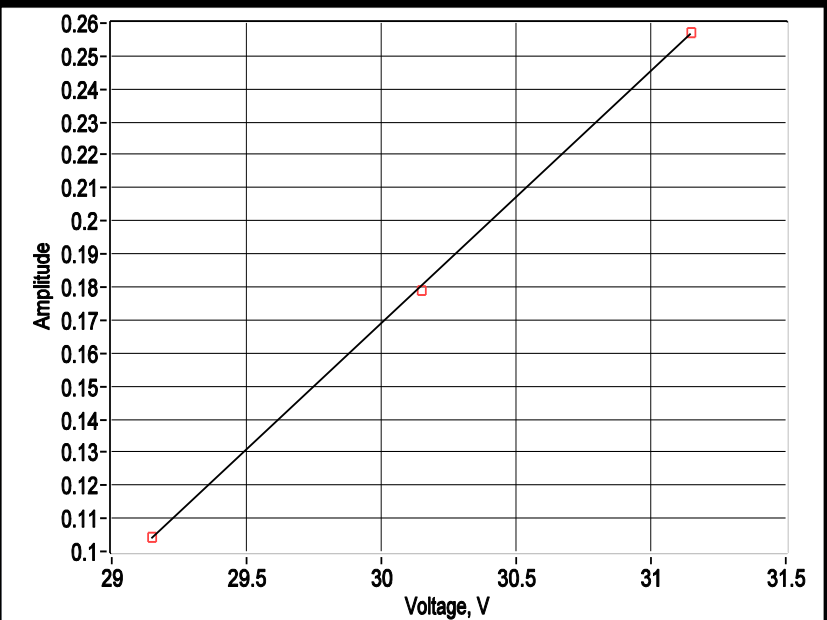
~20 p.e./mip from T956 extrude scint. bar read out by wls fiber.

Detailed characterization, under controlled climactic conditions reveal:

- A low , well-behaved break-down voltage V_{BD} varying with temperature as illustrated below



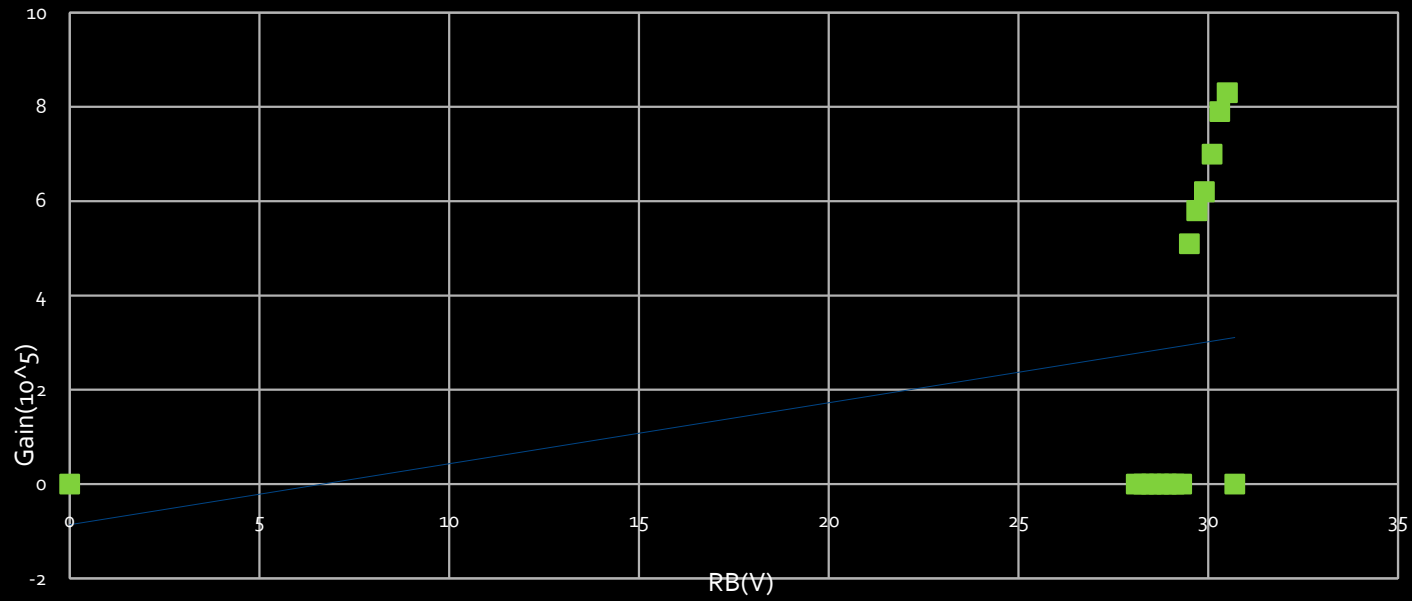
-- a dark count ranging between
 $\sim 10^4$ Hz at low temperatures and
 $\sim 10^6$ Hz at ambient temperatures



-and a gain of $\sim 10^6$ at ambient temperatures which varies linearly with bias voltage

The effects of γ and neutron radiation have also been studied and, as expected are not of concern at the larger radii occupied by the neutron counters

Gain vs Reverse Bias Voltage



PARAMETERS:

$Rq = 244k$

$Crq = 0.003pF$

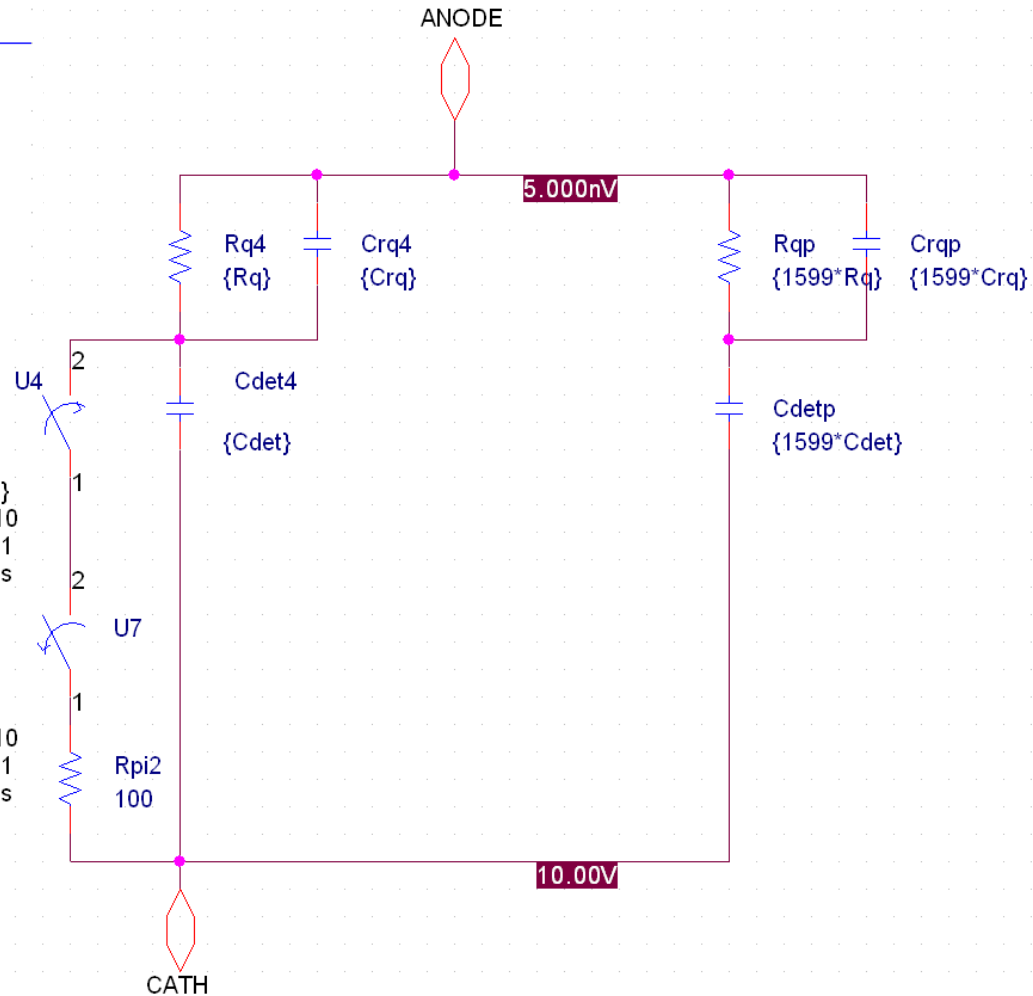
$Cdet = 0.03pF$

$ts = 1000ns$

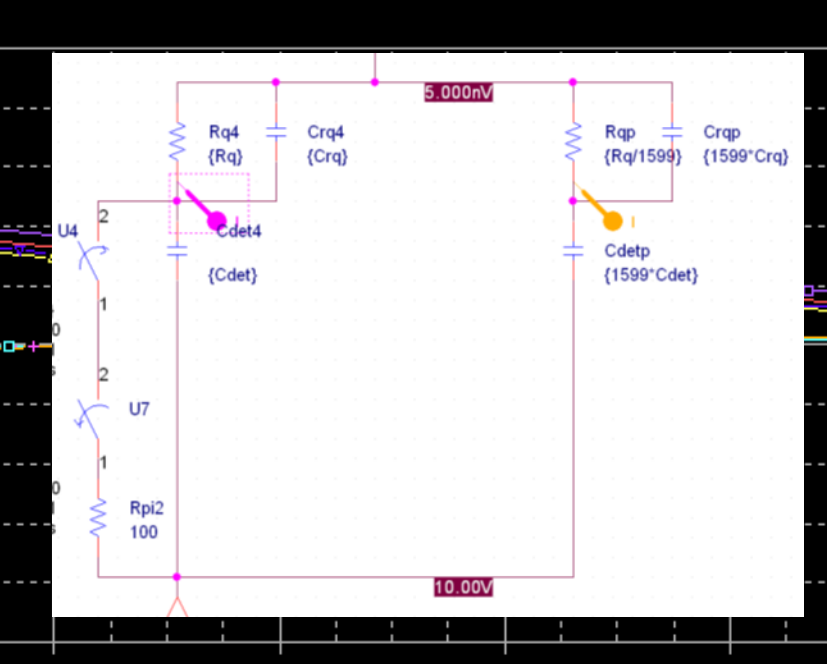
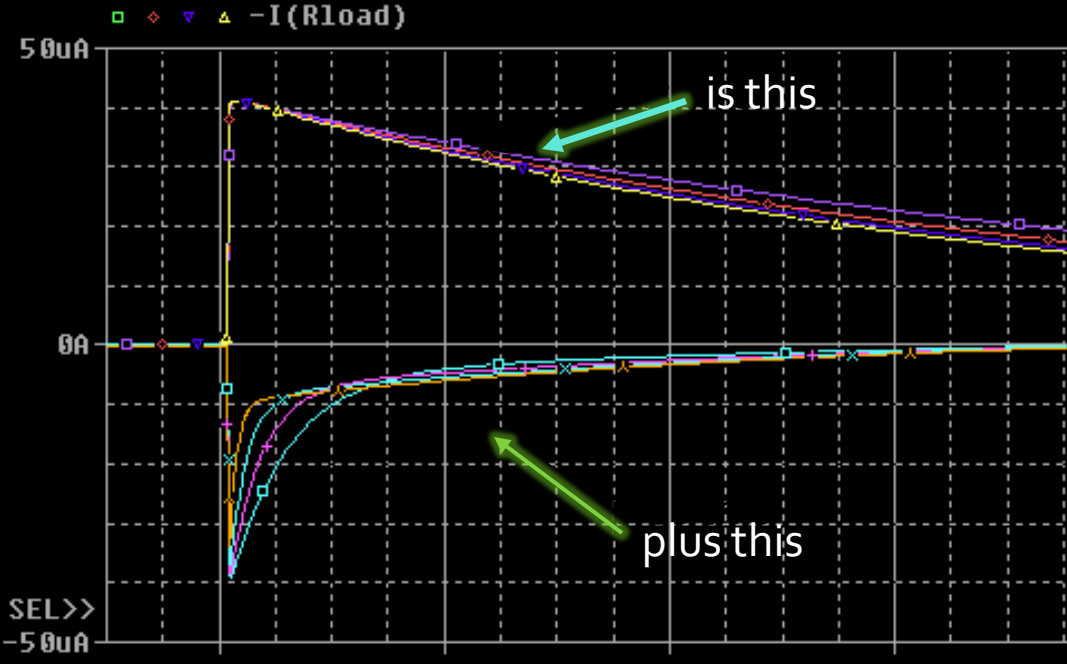
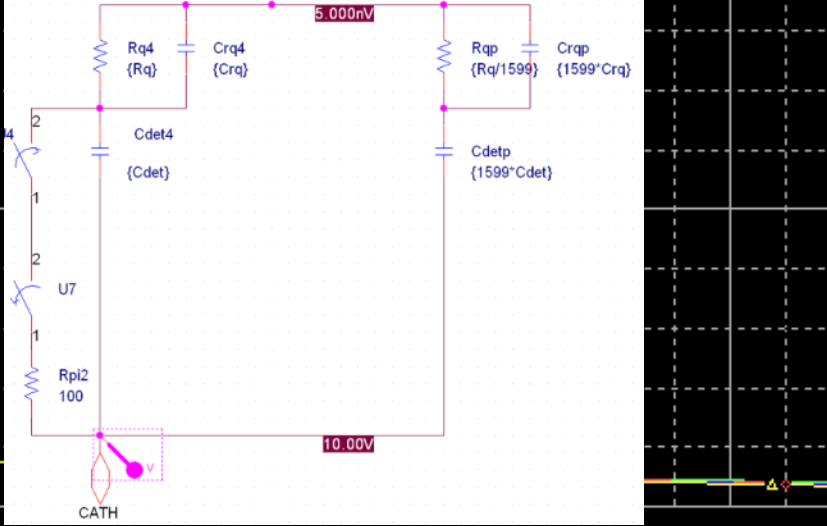
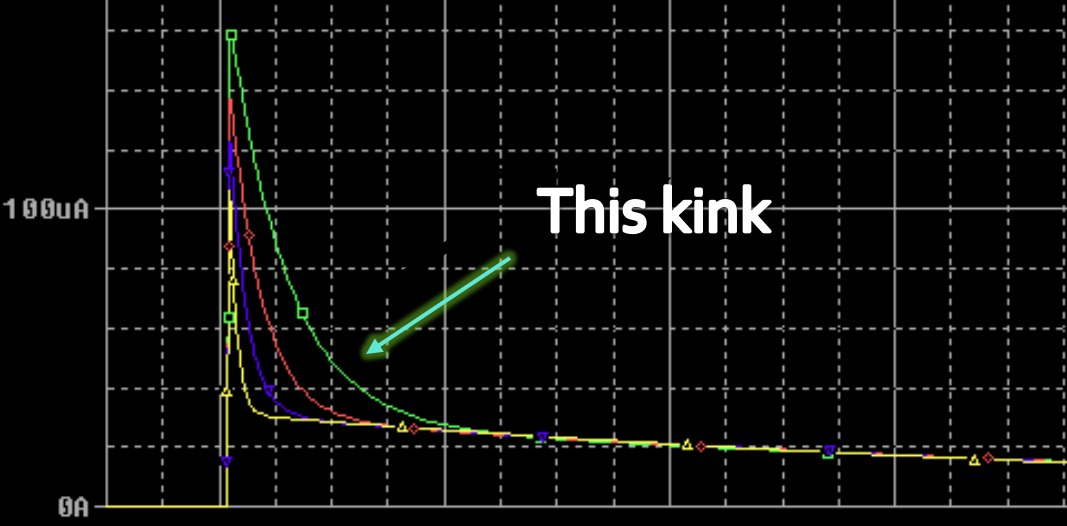
$tq = 1000.2ns$

$TCLOSE = \{ts\}$
 $RCLOSED = 10$
 $ROPEN = 1e11$
 $TTRAN = 0.1ns$

$TOPEN = \{tq\}$
 $RCLOSED = 10$
 $ROPEN = 1e11$
 $TTRAN = 0.1ns$



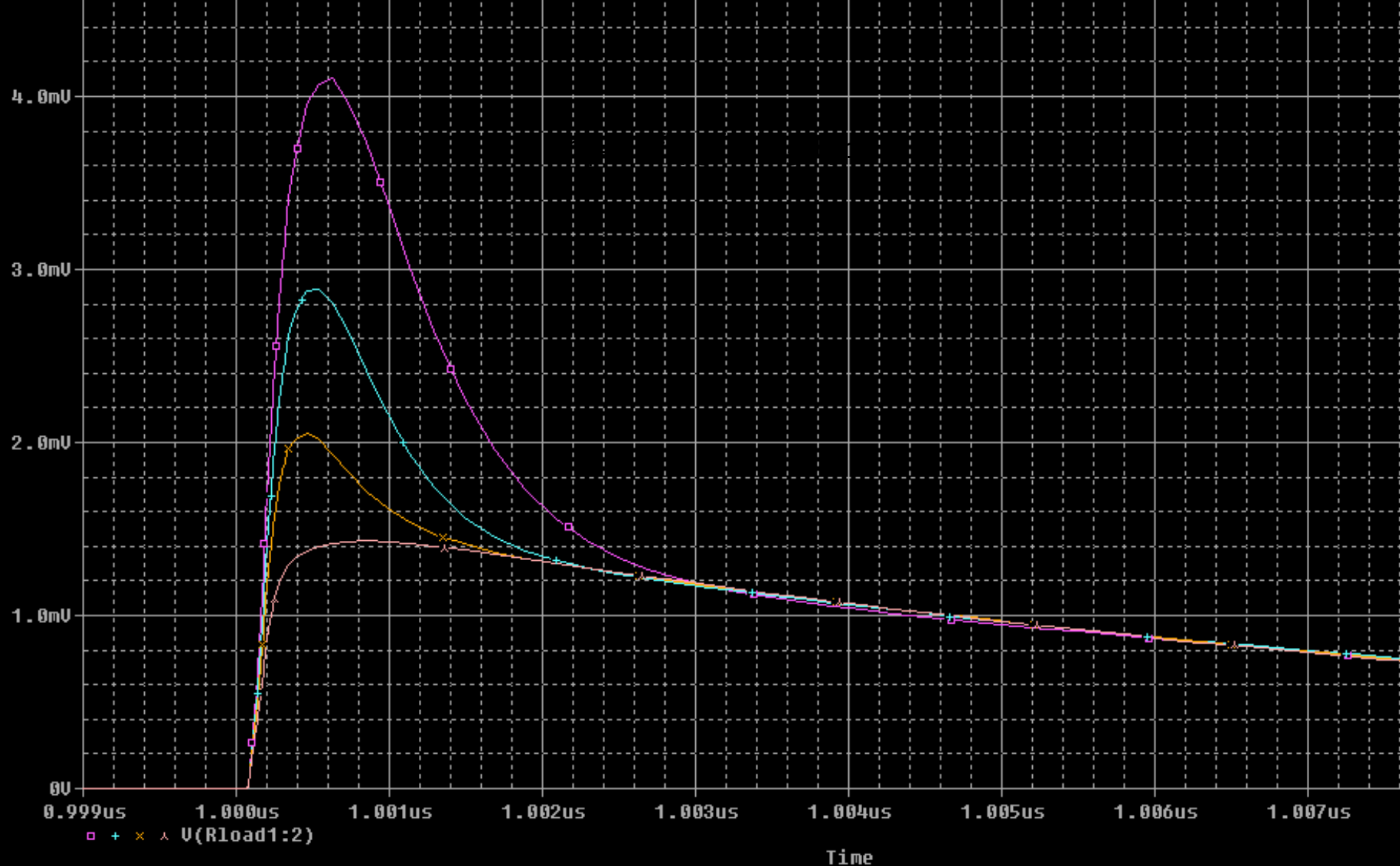
- This is the model I use. I got it from talks by C. Piemonte and others.
- Where available, I use parameters measured by Adam and co.
- Where not available, I guess and fiddle
- In my view, this sort of work is useful to develop a feel for things, and guide studies. Good predictions require a lot more work.



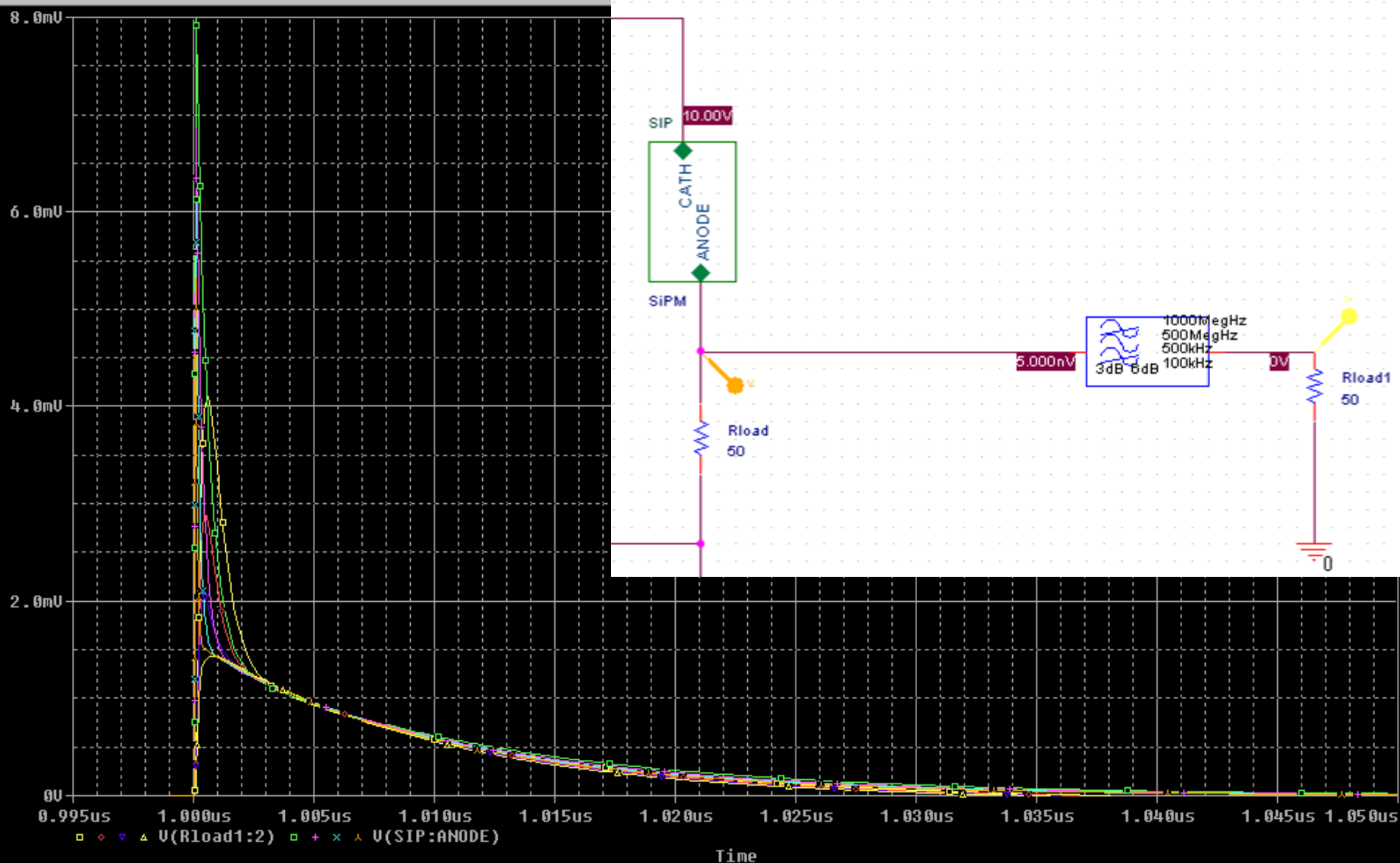
SEL>> 1.000us 1.002us 1.004us 1.006us 1.008us 1.010us 1.012us 1.014us

□ ◇ ▽ ▲ I(SIP.Rq4) □ + × ▲ I(SIP.Rqp)

Time



- The shape of the spike depends critically on the shaping function of the amplifier – you can also get “ripples”



- I think it makes sense to “integrate” this spike away before digitizing waveform

Readout of the SiPM

- I have seen the future of SiPM readout
 - Readout electronics **will be integrated into the SiPM!** because
 - SiPM is an inherently digital device
 - We digitize the signal from the SiPM
 - So why do we have an analog step in between?!?
 - Because we want to get started!

